

# MCF5208 ColdFire® Microprocessor Data Sheet

Supports MCF5207 & MCF5208

by: Microcontroller Division

The MCF5207 and MCF5208 devices are highly-integrated 32-bit microprocessors based on the version 2 ColdFire microarchitecture. Both devices contain a 16-Kbyte internal SRAM, an 8-Kbyte configurable cache, a 2-bank SDR/DDR SDRAM controller, a 16-channel DMA controller, up to three UARTs, a queued SPI, a low-power management mode module, and other peripherals that enable the MCF5207 and MCF5208 for use in industrial control and connectivity applications. The MCF5208 device also features a 10/100 Mbps fast ethernet controller.

This document provides detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications of the MCF5207 and MCF5208 microprocessors. It was written from the perspective of the MCF5208 device. See the following section for a summary of differences between the two devices.

## Table of Contents

1	MCF5207/8 Device Configurations.....	2
2	Ordering Information .....	3
3	Signal Descriptions.....	3
4	Mechanicals and Pinouts .....	8
5	Preliminary Electrical Characteristics .....	18
6	Revision History .....	43

# 1 MCF5207/8 Device Configurations

The following table compares the two devices described in this document:

**Table 1. MCF5207 & MCF5208 Configurations**

Module	MCF5207	MCF5208
Version 2 ColdFire Core with EMAC (Enhanced Multiply-Accumulate Unit)	x	x
Core (System) Clock	up to 166.67 MHz	
Peripheral and External Bus Clock (Core clock ÷ 2)	up to 83.33 MHz	
Performance (Dhrystone/2.1 MIPS)	up to 159	
Instruction/Data Cache	8 Kbytes	
Static RAM (SRAM)	16 Kbytes	
SDR/DDR SDRAM Controller	x	x
Fast Ethernet Controller (FEC)	—	x
Low-Power Management Module	x	x
UARTs	3	3
I <sup>2</sup> C	x	x
QSPI	x	x
32-bit DMA Timers	4	4
Watchdog Timer (WDT)	x	x
Periodic Interrupt Timers (PIT)	4	4
Edge Port Module (EPORT)	x	x
Interrupt Controllers (INTC)	1	1
16-channel Direct Memory Access (DMA)	x	x
FlexBus External Interface	x	x
General Purpose I/O Module (GPIO)	x	x
JTAG - IEEE <sup>®</sup> 1149.1 Test Access Port	x	x
Package	144 LQFP 144 MAPBGA	160 QFP 196 MAPBGA

## 2 Ordering Information

Table 2. Orderable Part Numbers

Freescale Part Number	Description	Speed	Temperature
MCF5207CAG166	MCF5207 RISC Microprocessor, 144 LQFP	166.67 MHz	-40° to +85° C
MCF5207CVM166	MCF5207 RISC Microprocessor, 144 MAPBGA	166.67 MHz	-40° to +85° C
MCF5208CAB166	MCF5208 RISC Microprocessor, 160 QFP	166.67 MHz	-40° to +85° C
MCF5208CVM166	MCF5208 RISC Microprocessor, 196 MAPBGA	166.67 MHz	-40° to +85° C

## 3 Signal Descriptions

The following table lists all the MCF5208 pins grouped by function. The “Dir” column is the direction for the primary function of the pin only. Refer to [Section 4, “Mechanicals and Pinouts,”](#) for package diagrams. For a more detailed discussion of the MCF5208 signals, consult the *MCF5208 Reference Manual* (MCF5208RM).

### NOTE

In this table and throughout this document a single signal within a group is designated without square brackets (i.e., A23), while designations for multiple signals within a group use brackets (i.e., A[23:21]) and is meant to include all signals within the two bracketed numbers when these numbers are separated by a colon.

### NOTE

The primary functionality of a pin is not necessarily its default functionality. Pins that are muxed with GPIO will default to their GPIO functionality.

Table 3. MCF5207/8 Signal Information and Muxing

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. <sup>1</sup>	MCF5207 144 LQFP	MCF5207 144 MAPBGA	MCF5208 160 QFP	MCF5208 196 MAPBGA
<b>Reset</b>								
$\overline{\text{RESET}}^2$	—	—	—	I	82	J10	90	J14
$\overline{\text{RSTOUT}}$	—	—	—	O	74	M12	82	N14
<b>Clock</b>								
EXTAL	—	—	—	I	78	K12	86	L14
XTAL	—	—	—	O	80	J12	88	K14
FB_CLK	—	—	—	O	34	L1	40	N1

## Signal Descriptions

**Table 3. MCF5207/8 Signal Information and Muxing (continued)**

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. <sup>1</sup>	MCF5207 144 LQFP	MCF5207 144 MAPBGA	MCF5208 160 QFP	MCF5208 196 MAPBGA
<b>Mode Selection</b>								
$\overline{\text{RCON}}^2$	—	—	—	I	144	C4	160	C3
DRAMSEL	—	—	—	I	79	H10	87	K11
<b>FlexBus</b>								
A[23:22]	—	$\overline{\text{FB\_CS}}[5:4]$	—	O	118, 117	B9, A10	126, 125	B11, A11
A[21:16]	—	—	—	O	116–114, 112, 108, 107	C9, A11, B10, A12, C11, B11	124, 123, 122, 120, 116, 115	B12, A12, A13, B13, B14, C13
A[15:14]	—	SD_BA[1:0]	—	O	106, 105	B12, C12	114, 113	C14, D12
A[13:11]	—	SD_A[13:11]	—	O	104–102	D11, E10, D12	112, 111, 110	D13, D14, E11
A10	—	—	—	O	101	C10	109	E12
A[9:0]	—	SD_A[9:0]	—	O	100–91	E11, D9, E12, F10, F11, E9, F12, G10, G12, F9	108–99	E13, E14, F11–F14, G11–G14
D[31:16]	—	SD_D[31:16] <sup>3</sup>	—	O	21–28, 40–47	F1, F2, G1, G2, G4, G3, H1, H2, K3, L2, L3, K2, M3, J4, M4, K4	27–34, 46–53	J4–J1, K4–K1, M3, N3, M4, N4, P4, L5, M5, N5
D[15:0]	—	FB_D[31:16] <sup>3</sup>	—	O	8–15, 51–58	B2, B1, C2, C1, D2, D1, E2, E1, L5, K5, L6, J6, M6, J7, L7, K7	16–23, 57–64	F3–F1, G4–G1, H1, N6, P6, L7, M7, N7, P7, N8, P8
$\overline{\text{BE}}/\overline{\text{BWE}}[3:0]$	PBE[3:0]	$\overline{\text{SD\_DQM}}[3:0]$	—	O	20, 48, 18, 50	F4, L4, E3, J5	26, 54, 24, 56	H2, P5, H4, M6
$\overline{\text{OE}}$	PBUSCTL3	—	—	O	60	J8	66	M8
$\overline{\text{TA}}^2$	PBUSCTL2	—	—	I	90	G11	98	H14
R/ $\overline{\text{W}}$	PBUSCTL1	—	—	O	59	K6	65	L8
$\overline{\text{TS}}$	PBUSCTL0	$\overline{\text{DACK0}}$	—	O	4	B3	12	E3
<b>Chip Selects</b>								
$\overline{\text{FB\_CS}}[3:2]$	PCS[3:2]	—	—	O	119, 120	D7, A9	—	C11, A10
$\overline{\text{FB\_CS1}}$	PCS1	$\overline{\text{SD\_CS1}}$	—	O	121	C8	127	B10
$\overline{\text{FB\_CS0}}$	—	—	—	O	122	B8	128	C10

Table 3. MCF5207/8 Signal Information and Muxing (continued)

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. <sup>1</sup>	MCF5207 144 LQFP	MCF5207 144 MAPBGA	MCF5208 160 QFP	MCF5208 196 MAPBGA
<b>SDRAM Controller</b>								
SD_A10	—	—	—	O	37	M1	43	N2
SD_CKE	—	—	—	O	6	C3	14	E1
SD_CLK	—	—	—	O	31	J1	37	L1
$\overline{\text{SD\_CLK}}$	—	—	—	O	32	K1	38	M1
$\overline{\text{SD\_CS0}}$	—	—	—	O	7	A1	15	F4
SD_DQS[3:2]	—	—	—	O	19, 49	F3, M5	25, 55	H3, L6
$\overline{\text{SD\_SCAS}}$	—	—	—	O	38	M2	44	P2
$\overline{\text{SD\_SRAS}}$	—	—	—	O	39	J2	45	P3
SD_SDR_DQS	—	—	—	O	29	H3	35	L3
$\overline{\text{SD\_WE}}$	—	—	—	O	5	D3	13	E2
<b>External Interrupts Port<sup>4</sup></b>								
$\overline{\text{IRQ7}}^2$	PIRQ7 <sup>2</sup>	—	—	I	134	A5	142	C7
$\overline{\text{IRQ4}}^2$	PIRQ4 <sup>2</sup>	$\overline{\text{DREQ0}}^2$	—	I	133	C6	141	D7
$\overline{\text{IRQ1}}^2$	PIRQ1 <sup>2</sup>	—	—	I	132	B6	140	D8
<b>FEC</b>								
FEC_MDC	PFECI2C3	I2C_SCL <sup>2</sup>	U2TXD	O	—	—	148	D6
FEC_MDIO	PFECI2C2	I2C_SDA <sup>2</sup>	U2RXD	I/O	—	—	147	C6
FEC_TXCLK	PFECH7	—	—	I	—	—	157	B3
FEC_TXEN	PFECH6	—	—	O	—	—	158	A2
FEC_TXD0	PFECH5	—	—	O	—	—	3	B1
FEC_COL	PFECH4	—	—	I	—	—	7	D3
FEC_RXCLK	PFECH3	—	—	I	—	—	154	B4
FEC_RXDV	PFECH2	—	—	I	—	—	153	A4
FEC_RXD0	PFECH1	—	—	I	—	—	152	D5
FEC_CRS	PFECH0	—	—	I	—	—	8	D2
FEC_TXD[3:1]	PFECL[7:5]	—	—	O	—	—	6–4	C1, C2, B2
FEC_TXER	PFECL4	—	—	O	—	—	156	A3
FEC_RXD[3:1]	PFECL[3:1]	—	—	I	—	—	149–151	A5, B5, C5
FEC_RXER	PFECL0	—	—	I	—	—	155	C4
<b>I<sup>2</sup>C</b>								
I2C_SDA <sup>2</sup>	PFECI2C0 <sup>2</sup>	U2RXD <sup>2</sup>	—	I/O	—	—	—	D1

## Signal Descriptions

**Table 3. MCF5207/8 Signal Information and Muxing (continued)**

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. <sup>1</sup>	MCF5207 144 LQFP	MCF5207 144 MAPBGA	MCF5208 160 QFP	MCF5208 196 MAPBGA
I2C_SCL <sup>2</sup>	PFECI2C1 <sup>2</sup>	U2TXD <sup>2</sup>	—	I/O	—	—	—	E4
<b>DMA</b>								
$\overline{DACK0}$ and $\overline{DREQ0}$ do not have a dedicated bond pads. Please refer to the following pins for muxing: $\overline{TS}$ and QSPI_CS2 for $\overline{DACK0}$ , IRQ4 and QSPI_DIN for $\overline{DREQ0}$ .								
<b>QSPI</b>								
QSPI_CS2	PQSPI3	$\overline{DACK0}$	$\overline{U2RTS}$	O	126	A8	132	D10
QSPI_CLK	PQSPI0	I2C_SCL <sup>2</sup>	—	O	127	C7	133	A9
QSPI_DOUT	PQSPI1	I2C_SDA <sup>2</sup>	—	O	128	A7	134	B9
QSPI_DIN	PQSPI2	$\overline{DREQ0}$ <sup>2</sup>	$\overline{U2CTS}$	I	129	B7	135	C9
<b>Note:</b> The QSPI_CS1 and QSPI_CS0 signals are available on the U1CTS, U1RTS, U0CTS, or U0RTS pins for the 196 and 160-pin packages.								
<b>UARTs</b>								
$\overline{U1CTS}$	PUARTL7	—	—	I	139	B4	—	—
$\overline{U1RTS}$	PUARTL6	—	—	O	142	A2	—	—
$\overline{U1CTS}$	PUARTL7	DT1IN	QSPI_CS1	I	—	—	136	D9
$\overline{U1RTS}$	PUARTL6	DT1OUT	QSPI_CS1	O	—	—	137	C8
U1TXD	PUARTL5	—	—	O	131	A6	139	A8
U1RXD	PUARTL4	—	—	I	130	D6	138	B8
$\overline{U0CTS}$	PUARTL3	—	—	I	140	E4	—	—
$\overline{U0RTS}$	PUARTL2	—	—	O	141	D5	—	—
$\overline{U0CTS}$	PUARTL3	DT0IN	QSPI_CS0	I	—	—	76	N12
$\overline{U0RTS}$	PUARTL2	DT0OUT	QSPI_CS0	O	—	—	77	P12
U0TXD	PUARTL1	—	—	O	71	L10	79	P13
U0RXD	PUARTL0	—	—	I	70	M10	78	N13
<b>Note:</b> The UART2 signals are multiplexed on the DMA Timers, QSPI, FEC, and I2C pins.								
<b>DMA Timers</b>								
DT3IN	PTIMER3	DT3OUT	$\overline{U2CTS}$	I	135	B5	143	B7
DT2IN	PTIMER2	DT2OUT	$\overline{U2RTS}$	I	136	C5	144	A7
DT1IN	PTIMER1	DT1OUT	U2RXD	I	137	A4	145	A6
DT0IN	PTIMER0	DT0OUT	U2TXD	I	138	A3	146	B6
<b>BDM/JTAG<sup>5</sup></b>								
JTAG_EN <sup>6</sup>	—	—	—	I	83	J11	91	J13
DSCLK	—	$\overline{TRST}$ <sup>2</sup>	—	I	76	K11	84	L12

Table 3. MCF5207/8 Signal Information and Muxing (continued)

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. <sup>1</sup>	MCF5207 144 LQFP	MCF5207 144 MAPBGA	MCF5208 160 QFP	MCF5208 196 MAPBGA
PSTCLK	—	TCLK <sup>2</sup>	—	O	64	M7	70	P9
BKPT	—	TMS <sup>2</sup>	—	I	75	L12	83	M14
DSI	—	TDI <sup>2</sup>	—	I	77	H9	85	K12
DSO	—	TDO	—	O	69	M9	75	M12
DDATA[3:0]	—	—	—	O	—	K9, L9, M11, M8	—	P11, N11, M11, P10
PST[3:0]	—	—	—	O	—	L11, L8, K10, K8	—	N10, M10, L10, L9
ALLPST	—	—	—	O	67	—	73	—
<b>Test</b>								
TEST <sup>6</sup>	—	—	—	I	109	—	—	C12
PLL_TEST	—	—	—	I	—	—	—	M13
<b>Power Supplies</b>								
EVDD	—	—	—		1, 63, 66, 72, 81, 87, 125	E5–E6, F5, G8–G9, H7–H8	2, 9, 69, 72, 80, 89, 95, 131	E5–E7, F5, F6, G5, H10, J9, J10, K8–K10, K13, M9
IVDD	—	—	—		30, 68, 84, 113, 143	D4, D8, H4, H11, J9	36, 74, 92, 121, 159	J12, D4, D11, H11, L4, L11,
PLL_VDD	—	—	—		86	H12	94	H13
SD_VDD	—	—	—		3, 17, 33, 35, 61, 89, 110, 123	E7–E8, F8, G5, H5–H6, J3	11, 39, 41, 67, 97, 118, 129	E8–E10, F9, F10, G10, H5, J5, J6, K5–K7, L2
VSS	—	—	—		2, 16, 36, 62, 65, 73, 88, 111, 124	D10, F6–F7, G6–G7	1, 10, 42, 68, 71, 81, 96, 117, 119, 130	A1, A14, F7–F8, G6–G9, H6–H9, J7–J8, L13, M2, N9, P1, P14
PLL_VSS	—	—	—		85	—	93	H12

## NOTES:

<sup>1</sup> Refers to pin's primary function.

<sup>2</sup> Pull-up enabled internally on this signal for this mode.

<sup>3</sup> Primary functionality selected by asserting the DRAMSEL signal (SDR mode). Alternate functionality selected by negating the DRAMSEL signal (DDR mode). The GPIO module is not responsible for assigning these pins.

<sup>4</sup> GPIO functionality is determined by the edge port module. The GPIO module is only responsible for assigning the alternate functions.

---

## Mechanicals and Pinouts

- <sup>5</sup> If JTAG\_EN is asserted, these pins default to Alternate 1 (JTAG) functionality. The GPIO module is not responsible for assigning these pins.
- <sup>6</sup> Pull-down enabled internally on this signal for this mode.

# 4 Mechanicals and Pinouts

This section contains drawings showing the pinout and the packaging and mechanical characteristics of the MCF5207 and MCF5208 devices.

### NOTE

The mechanical drawings are the latest revisions at the time of publication of this document. The most up-to-date mechanical drawings can be found at the product summary page located at <http://www.freescale.com/coldfire>.



# 4.1 Pinout—144 LQFP

Figure 1 shows a pinout of the MCF5207CAG166 device.

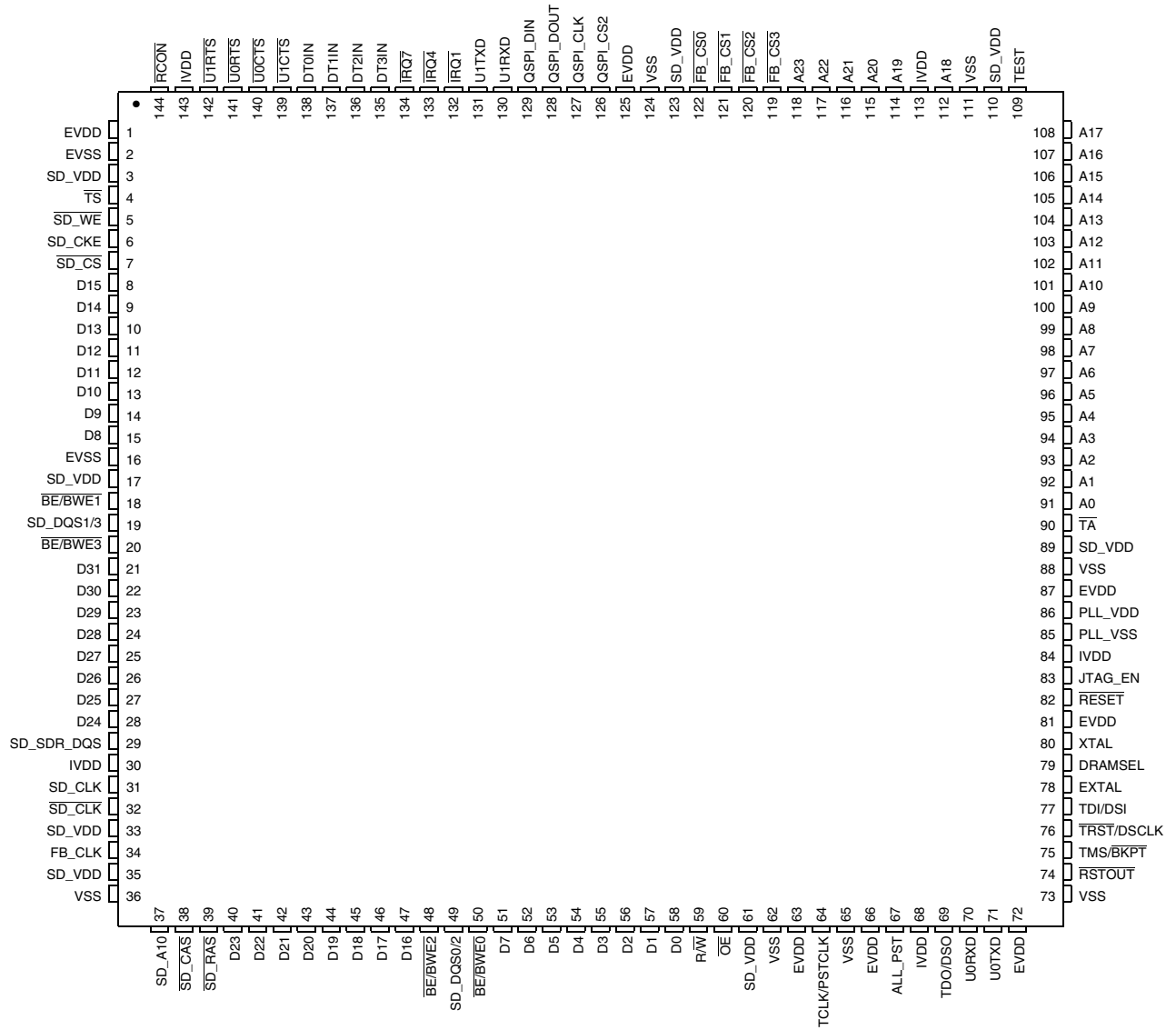


Figure 1. MCF5207CAG166 Pinout Top View (144 LQFP)

## 4.2 Package Dimensions—144 LQFP

Figure 2 and Figure 3 show MCF5207CAB166 package dimensions.

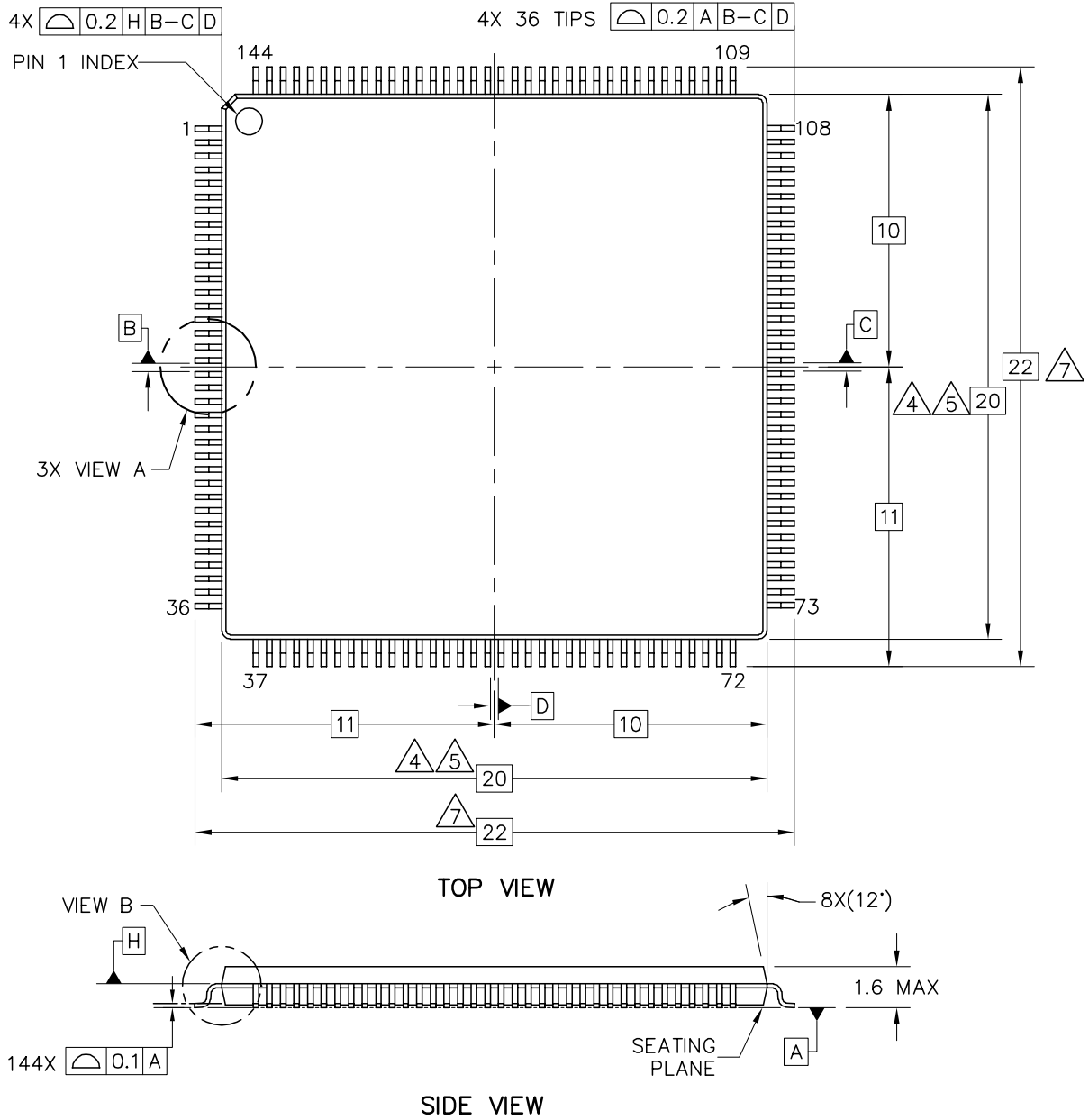
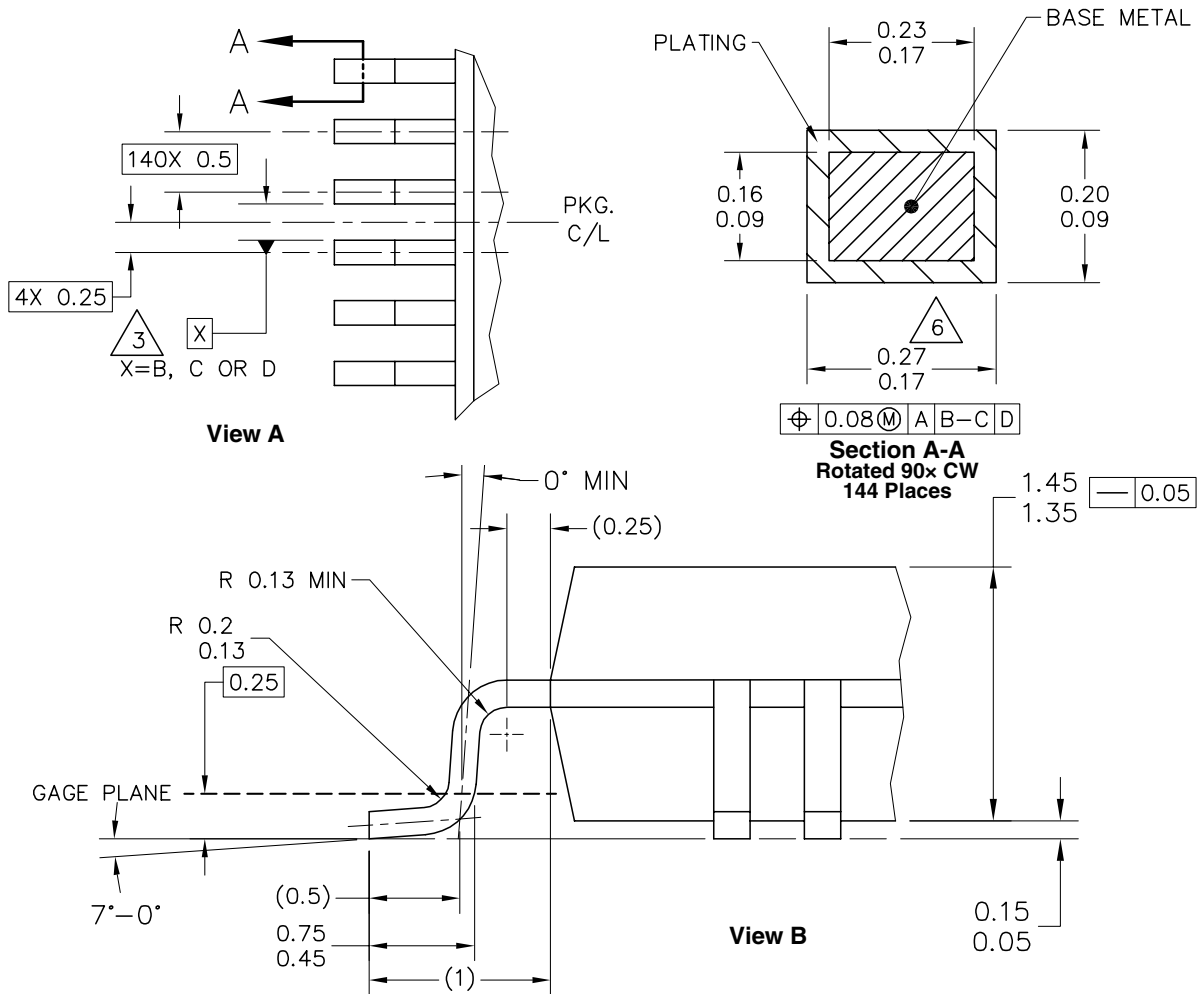


Figure 2. MCF5207CAB166 Package Dimensions (Sheet 1 of 2)



NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUMS B, C AND D TO BE DETERMINED AT DATUM PLANE H.
4. THE TOP PACKAGE BODY SIZE MAY BE SMALLER THAN THE BOTTOM PACKAGE SIZE BY A MAXIMUM OF 0.1 mm.
5. THIS DIMENSIONS DO NOT INCLUDE MOLD PROTRUSIONS. THE MAXIMUM ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSIONS ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.
6. THIS DIMENSION DOES NOT INCLUDE DAM BAR PROTRUSION. PROTRUSIONS SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.35. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD SHALL BE 0.07 mm.
7. THIS DIMENSIONS ARE DETERMINED AT THE SEATING PLANE, DATUM A.

**Figure 3. MCF5207CAB166 Package Dimensions (Sheet 2 of 2)**

### 4.3 Pinout—144 MAPBGA

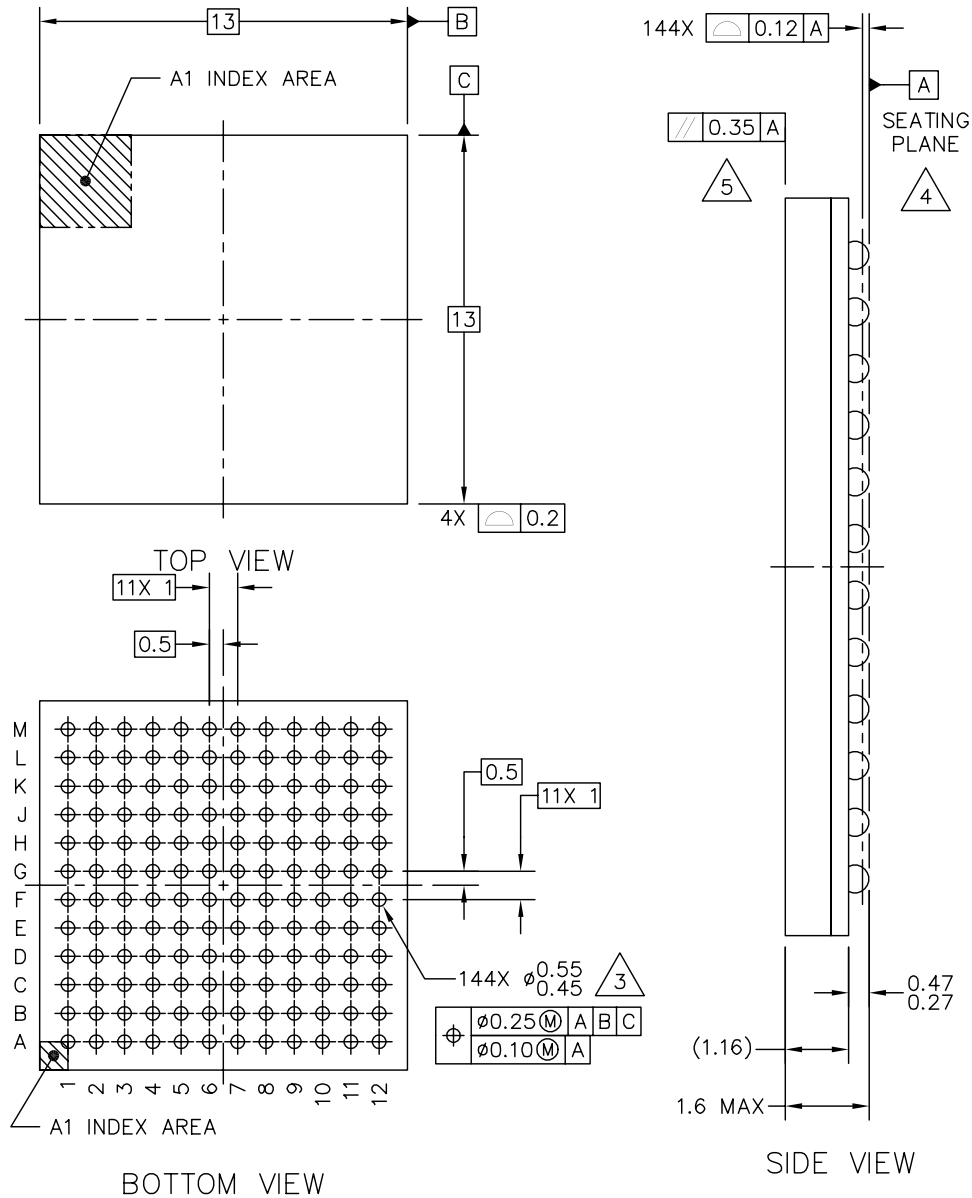
The pinout of the MCF5207CVM166 device is shown below.

	1	2	3	4	5	6	7	8	9	10	11	12	
A	$\overline{\text{SD\_CS}}$	$\overline{\text{U1RTS}}$	DT0IN	DT1IN	$\overline{\text{IRQ7}}$	U1TXD	QSPI_DOUT	QSPI_CS2	$\overline{\text{FB\_CS2}}$	A22	A20	A18	A
B	D14	D15	$\overline{\text{TS}}$	$\overline{\text{U1CTS}}$	DT3IN	$\overline{\text{IRQ1}}$	QSPI_DIN	$\overline{\text{FB\_CS0}}$	A23	A19	A16	A15	B
C	D12	D13	SD_CKE	$\overline{\text{RCON}}$	DT2IN	$\overline{\text{IRQ4}}$	QSPI_CLK	$\overline{\text{FB\_CS1}}$	A21	A10	A17	A14	C
D	D10	D11	$\overline{\text{SD\_WE}}$	IVDD	$\overline{\text{U0RTS}}$	U1RXD	$\overline{\text{FB\_CS3}}$	IVDD	A8	VSS	A13	A11	D
E	D8	D9	$\overline{\text{BE/BWE1}}$	$\overline{\text{U0CTS}}$	EVDD	EVDD	SD_VDD	SD_VDD	A4	A12	A9	A7	E
F	D31	D30	SD_DQS1	$\overline{\text{BE/BWE3}}$	EVDD	VSS	VSS	SD_VDD	A0	A6	A5	A3	F
G	D29	D28	D26	D27	SD_VDD	VSS	VSS	EVDD	EVDD	A2	$\overline{\text{TA}}$	A1	G
H	D25	D24	SD_SDR_DQS	IVDD	SD_VDD	SD_VDD	EVDD	EVDD	TDI/DSI	DRAM SEL	IVDD	PLL_VDD	H
J	SD_CLK	$\overline{\text{SD\_RAS}}$	SD_VDD	D18	$\overline{\text{BE/BWE0}}$	D4	D2	$\overline{\text{OE}}$	IVDD	$\overline{\text{RESET}}$	JTAG_EN	XTAL	J
K	$\overline{\text{SD\_CLK}}$	D20	D23	D16	D6	R/ $\overline{\text{W}}$	D0	PST0	DDATA3	PST1	$\overline{\text{TRST/DSCLK}}$	EXTAL	K
L	FB_CLK	D22	D21	$\overline{\text{BE/BWE2}}$	D7	D5	D1	PST2	DDATA2	U0TXD	PST3	$\overline{\text{TMS/BKPT}}$	L
M	SD_A10	$\overline{\text{SD\_CAS}}$	D19	D17	SD_DQS0	D3	TCLK/PSTCLK	DDATA0	TDO/DSO	U0RXD	DDATA1	$\overline{\text{RSTOUT}}$	M
	1	2	3	4	5	6	7	8	9	10	11	12	

Figure 4. MCF5207CVM166 Pinout Top View (144 MAPBGA)

## 4.4 Package Dimensions—144 MAPBGA

Figure 5 shows the MCF5207CAB166 package dimensions.



NOTES:

1. ALL DIMENSIONS IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. MAXIMUM SOLDER BALL DIAMETER MEASURED PARALLEL TO DATUM A.
4. DATUM A, THE SEATING PLANE, IS DETERMINED BY THE SPHERICAL CROWNS OF THE SOLDER BALLS.
5. PARALLELISM MEASUREMENT SHALL EXCLUDE ANY EFFECT OF MARK ON TOP SURFACE OF PACKAGE.

**Figure 5. MCF5207CAB166 Package Dimensions (144 MAPBGA)**

# 4.5 Pinout—160 QFP

Figure 6 shows a pinout of the MCF5208CAB166 device.

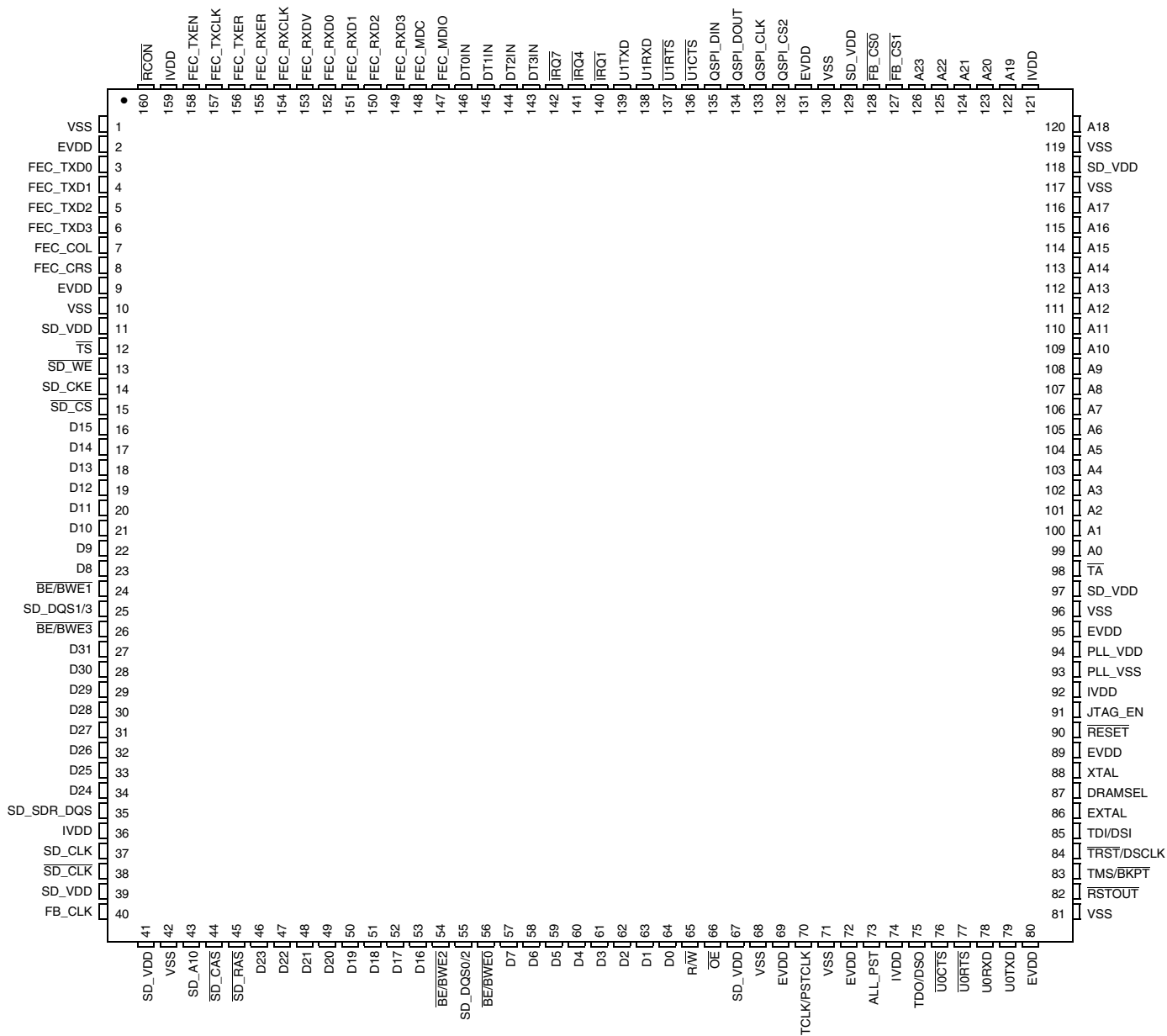


Figure 6. MCF5208CAB166 Pinout Top View (160 QFP)

## 4.6 Package Dimensions—160 QFP

The package dimensions of the MCF5208CAB166 device are shown in the figures below.

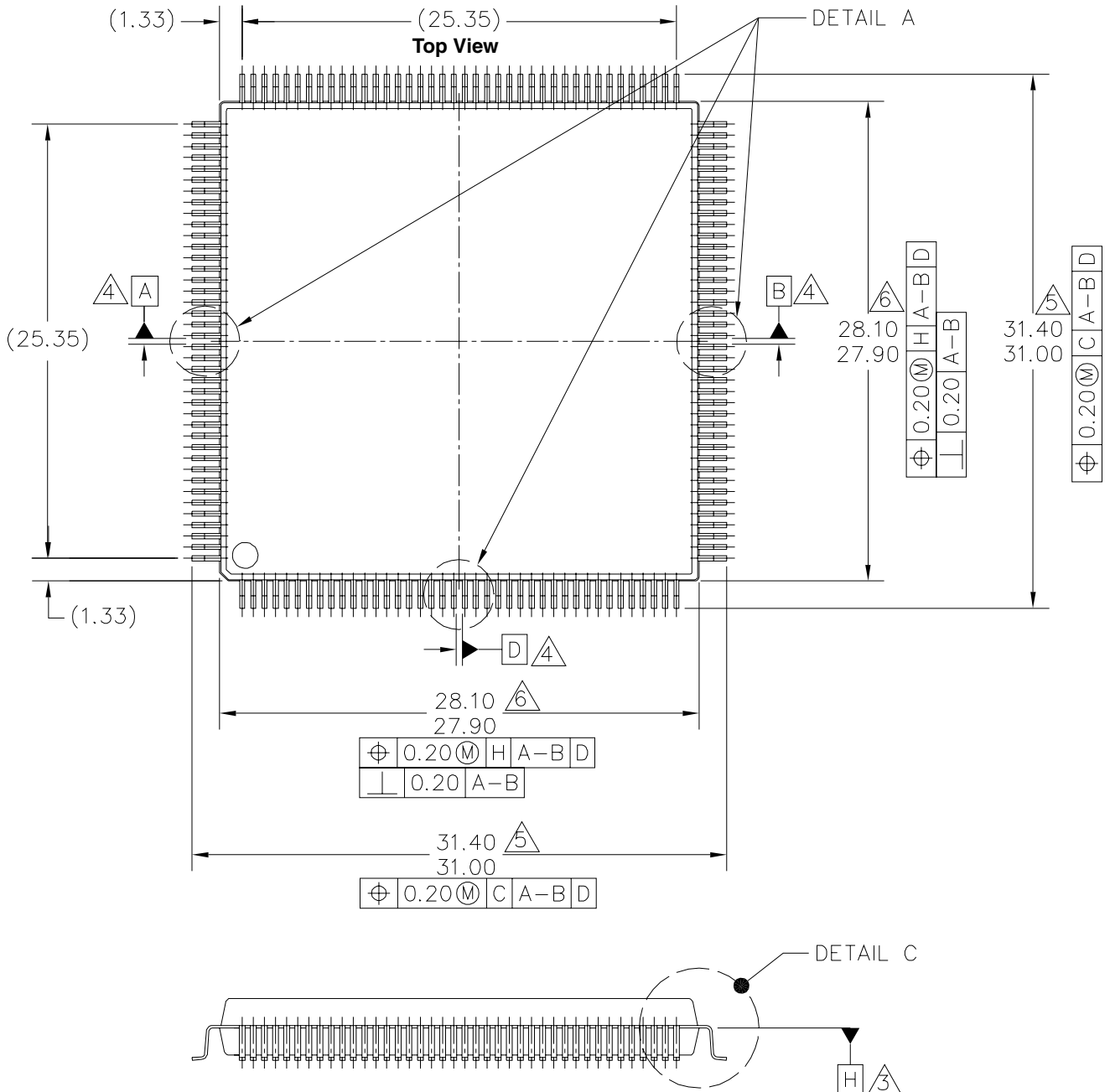
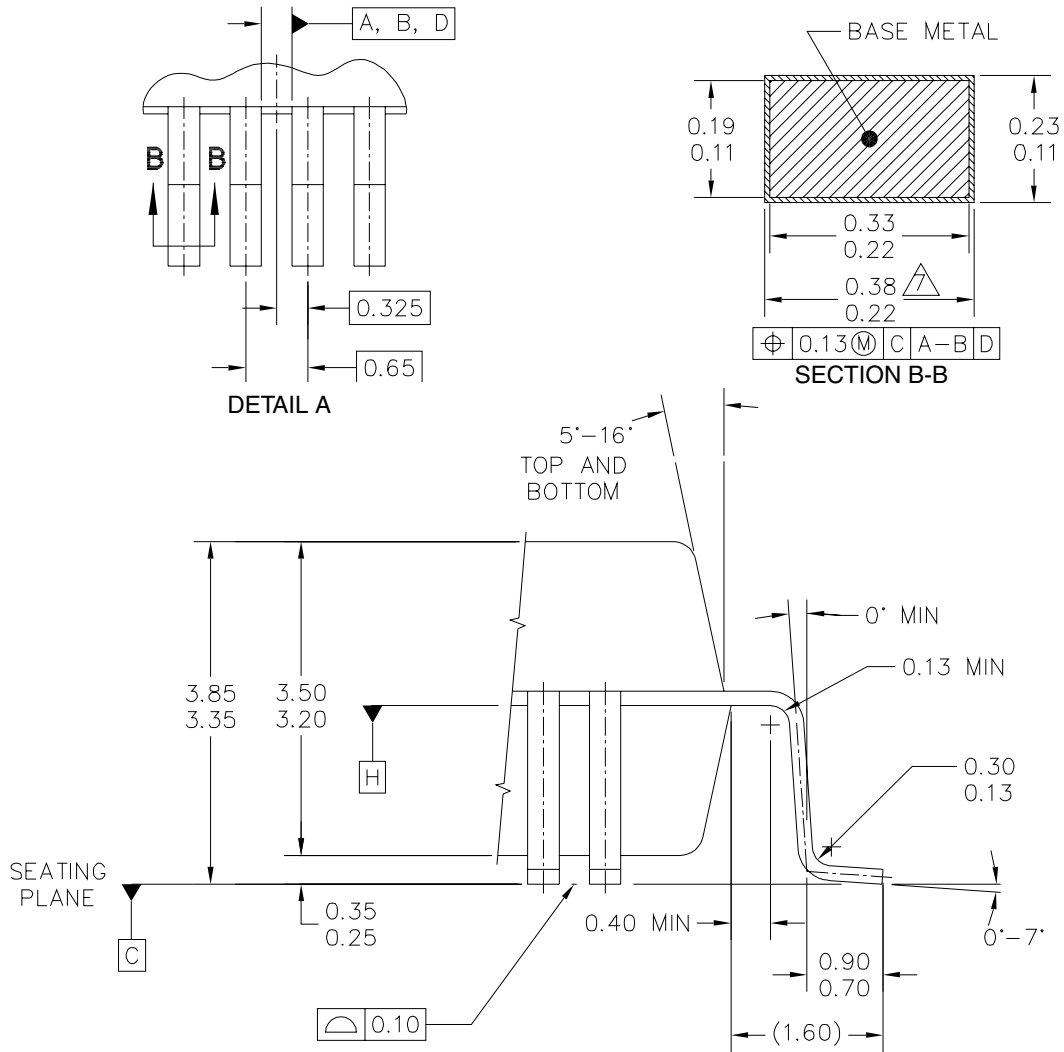


Figure 7. MCF5208CAB166 Package Dimensions (Sheet 1 of 2)

**Mechanicals and Pinouts**



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
- △ 3 DATUM PLANE IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
- △ 4 DATUMS TO BE DETERMINED AT DATUM PLANE H.
- △ 5 DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
- △ 6 DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 PER SIDE. DIMENSIONS DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
- △ 7 DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.

**Figure 8. MCF5208CAB166 Package Dimensions (Sheet 2 of 2)**



## 4.7 Pinout—196 MAPBGA

Figure 6 shows a pinout of the MCF5208CVM166 device.

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	
A	VSS	FEC_TXEN	FEC_TXER	FEC_RXDV	FEC_RXD3	DT1IN	DT2IN	U1TXD	QSPI_CLK	FB_CS2	A22	A20	A19	VSS	A
B	FEC_TXD0	FEC_TXD1	FEC_TXCLK	FEC_RXCLK	FEC_RXD2	DT0IN	DT3IN	U1RXD	QSPI_DOUT	FB_CS1	A23	A21	A18	A17	B
C	FEC_TXD3	FEC_TXD2	RCON	FEC_RXER	FEC_RXD1	FEC_MDIO	IRQ7	U1RTS	QSPI_DIN	FB_CS0	FB_CS3	TEST	A16	A15	C
D	I2C_SDA	FEC_CRS	FEC_COL	IVDD	FEC_RXD0	FEC_MDC	IRQ4	IRQ1	U1CTS	QSPI_CS2	IVDD	A14	A13	A12	D
E	SD_CKE	SD_WE	TS	I2C_SCL	EVDD	EVDD	EVDD	SD_VDD	SD_VDD	SD_VDD	A11	A10	A9	A8	E
F	D13	D14	D15	SD_CS	EVDD	EVDD	VSS	VSS	SD_VDD	SD_VDD	A7	A6	A5	A4	F
G	D9	D10	D11	D12	EVDD	VSS	VSS	VSS	VSS	SD_VDD	A3	A2	A1	A0	G
H	D8	BE/BWE3	SD_DQS1	BE/BWE1	SD_VDD	VSS	VSS	VSS	VSS	EVDD	IVDD	PLL_VSS	PLL_VDD	TA	H
J	D28	D29	D30	D31	SD_VDD	SD_VDD	VSS	VSS	EVDD	EVDD	NC	IVDD	JTAG_EN	RESET	J
K	D24	D25	D26	D27	SD_VDD	SD_VDD	SD_VDD	EVDD	EVDD	EVDD	DRAM_SEL	TDI/DSI	EVDD	XTAL	K
L	SD_CLK	SD_VDD	SD_DR_DQS	IVDD	D18	SD_DQS0	D5	RW	PST0	PST1	IVDD	TRST/DSCLK	VSS	EXTAL	L
M	SD_CLK	VSS	D23	D21	D17	BE/BWE0	D4	OE	EVDD	PST2	DDATA1	TDO/DSO	PLL_TEST	TMS/BKPT	M
N	FB_CLK	SD_A10	D22	D20	D16	D7	D3	D1	VSS	PST3	DDATA2	U0CTS	U0RXD	RSTOUT	N
P	VSS	SD_CAS	SD_RAS	D19	BE/BWE2	D6	D2	D0	TCLK/PSTCLK	DDATA0	DDATA3	U0RTS	U0TXD	VSS	P
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	

Figure 9. MCF5208CVM166 Pinout Top View (196 MAPBGA)

## 4.8 Package Dimensions—196 MAPBGA

The package dimensions for the MCF5208CVM166 device is shown below.

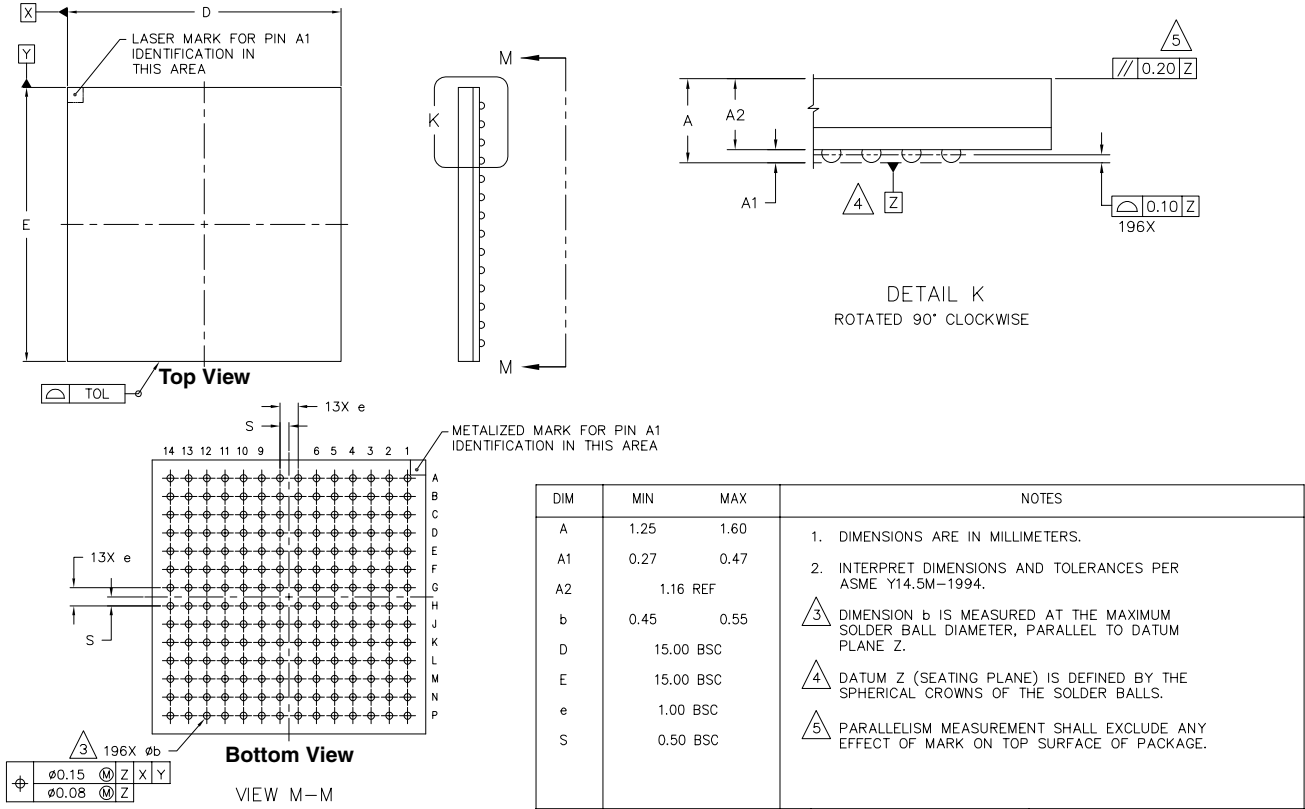


Figure 10. MCF5208CVM166 Package Dimensions (196 MAPBGA)

## 5 Preliminary Electrical Characteristics

The following electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle, however for production silicon these specifications will be met. Finalized specifications will be published after complete characterization and device qualifications have been completed.

### 5.1 Maximum Ratings

Table 4. Absolute Maximum Ratings<sup>1, 2</sup>

Rating	Symbol	Value	Unit
Core Supply Voltage	$IV_{DD}$	- 0.5 to +2.0	V
CMOS Pad Supply Voltage	$EV_{DD}$	- 0.3 to +4.0	V
DDR/Memory Pad Supply Voltage	$SDV_{DD}$	- 0.3 to +4.0	V
PLL Supply Voltage	$PLL_{V_{DD}}$	- 0.3 to +2.0	V

**Table 4. Absolute Maximum Ratings<sup>1, 2</sup> (continued)**

Digital Input Voltage <sup>3</sup>	$V_{IN}$	- 0.3 to +3.6	V
Instantaneous Maximum Current Single pin limit (applies to all pins) <sup>3, 4, 5</sup>	$I_D$	25	mA
Operating Temperature Range (Packaged)	$T_A$ ( $T_L - T_H$ )	- 40 to 85	°C
Storage Temperature Range	$T_{stg}$	- 55 to 150	°C

## NOTES:

- <sup>1</sup> Functional operating conditions are given in [Section 5.4, “DC Electrical Specifications.”](#) Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Continued operation at these levels may affect device reliability or cause permanent damage to the device.
- <sup>2</sup> This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $EV_{DD}$ ).
- <sup>3</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.
- <sup>4</sup> All functional non-supply pins are internally clamped to  $V_{SS}$  and  $EV_{DD}$ .
- <sup>5</sup> Power supply must maintain regulation within operating  $EV_{DD}$  range during instantaneous and operating maximum current conditions. If positive injection current ( $V_{in} > EV_{DD}$  is greater than  $I_{DD}$ , the injection current may flow out of  $EV_{DD}$  and could result in external power supply going out of regulation. Insure external  $EV_{DD}$  load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power (ex; no clock). Power supply must maintain regulation within operating  $EV_{DD}$  range during instantaneous and operating maximum current conditions.

## 5.2 Thermal Characteristics

[Table 5](#) lists thermal resistance values

**Table 5. Thermal Characteristics**

Characteristic		Symbol	196MBGA	160QFP	Unit
Junction to ambient, natural convection	Four layer board (2s2p)	$\theta_{JMA}$	32 <sup>1,2</sup>	40 <sup>1,2</sup>	°C/W
Junction to ambient (@200 ft/min)	Four layer board (2s2p)	$\theta_{JMA}$	29 <sup>1,2</sup>	36 <sup>1,2</sup>	°C/W
Junction to board		$\theta_{JB}$	20 <sup>3</sup>	25 <sup>3</sup>	°C/W
Junction to case		$\theta_{JC}$	10 <sup>4</sup>	10 <sup>4</sup>	°C/W
Junction to top of package		$\Psi_{jt}$	2 <sup>1,5</sup>	2 <sup>1,5</sup>	°C/W
Maximum operating junction temperature		$T_j$	105	105	°C

## Preliminary Electrical Characteristics

### NOTES:

- <sup>1</sup>  $\theta_{JMA}$  and  $\Psi_{jt}$  parameters are simulated in conformance with EIA/JESD Standard 51-2 for natural convection. Freescale recommends the use of  $\theta_{JMA}$  and power dissipation specifications in the system design to prevent device junction temperatures from exceeding the rated specification. System designers should be aware that device junction temperatures can be significantly influenced by board layout and surrounding devices. Conformance to the device junction temperature specification can be verified by physical measurement in the customer's system using the  $\Psi_{jt}$  parameter, the device power dissipation, and the method described in EIA/JESD Standard 51-2.
- <sup>2</sup> Per JEDEC JESD51-6 with the board horizontal.
- <sup>3</sup> Thermal resistance between the die and the printed circuit board in conformance with JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- <sup>4</sup> Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- <sup>5</sup> Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written in conformance with Psi-JT.

The average chip-junction temperature ( $T_J$ ) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JMA}) \quad \text{Eqn. 1}$$

Where:

$T_A$  = Ambient Temperature, °C

$\theta_{JMA}$  = Package Thermal Resistance, Junction-to-Ambient, °C/W

$P_D$  =  $P_{INT} + P_{I/O}$

$P_{INT}$  =  $I_{DD} \times IV_{DD}$ , Watts - Chip Internal Power

$P_{I/O}$  = Power Dissipation on Input and Output Pins - User Determined

For most applications  $P_{I/O} < P_{INT}$  and can be ignored. An approximate relationship between  $P_D$  and  $T_J$  (if  $P_{I/O}$  is neglected) is:

$$P_D = \frac{K}{(T_J + 273^\circ C)} \quad \text{Eqn. 2}$$

Solving equations 1 and 2 for K gives:

$$K = P_D \times (T_A \times 273^\circ C) + \theta_{JMA} \times P_D^2 \quad \text{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from [Equation 3](#) by measuring  $P_D$  (at equilibrium) for a known  $T_A$ . Using this value of K, the values of  $P_D$  and  $T_J$  can be obtained by solving [Equation 1](#) and [Equation 2](#) iteratively for any value of  $T_A$ .

## 5.3 ESD Protection

Table 6. ESD Protection Characteristics<sup>1, 2</sup>

Characteristics	Symbol	Value	Units
ESD Target for Human Body Model	HBM	2000	V

NOTES:

- <sup>1</sup> All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
- <sup>2</sup> A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing is performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

## 5.4 DC Electrical Specifications

Table 7. DC Electrical Specifications

Characteristic	Symbol	Min	Max	Unit
Core Supply Voltage	$IV_{DD}$	1.4	1.6	V
PLL Supply Voltage	$PLL_{V_{DD}}$	1.4	1.6	V
CMOS Pad Supply Voltage	$EV_{DD}$	3.0	3.6	V
Mobile DDR/Bus Pad Supply Voltage	$SDV_{DD}$	1.65	1.95	V
DDR/Bus Pad Supply Voltage	$SDV_{DD}$	2.25	2.75	V
SDR/Bus Pad Supply Voltage	$SDV_{DD}$	3.0	3.6	V
CMOS Input High Voltage	$EV_{IH}$	2	$EV_{DD} + 0.05$	V
CMOS Input Low Voltage	$EV_{IL}$	-0.05	0.8	V
Mobile DDR/Bus Input High Voltage	$SDV_{IH}$	TBD	$SDV_{DD} + 0.05$	V
Mobile DDR/Bus Input Low Voltage	$SDV_{IL}$	-0.05	TBD	V
DDR/Bus Input High Voltage	$SDV_{IH}$	2	$SDV_{DD} + 0.05$	V
DDR/Bus Input Low Voltage	$SDV_{IL}$	-0.05	0.8	V
Input Leakage Current $V_{in} = IV_{DD}$ or $V_{SS}$ , Input-only pins	$I_{in}$	-1.0	1.0	$\mu A$
CMOS Output High Voltage $I_{OH} = -5.0$ mA	$EV_{OH}$	$EV_{DD} - 0.4$	—	V
CMOS Output Low Voltage $I_{OL} = 5.0$ mA	$EV_{OL}$	—	0.4	V
DDR/Bus Output High Voltage $I_{OH} = -5.0$ mA	$SDV_{OH}$	$SDV_{DD} - 0.4$	—	V
DDR/Bus Output Low Voltage $I_{OL} = 5.0$ mA	$SDV_{OL}$	—	0.4	V
Weak Internal Pull Up Device Current, tested at $V_{IL}$ Max. <sup>1</sup>	$I_{APU}$	-10	-130	$\mu A$

Table 7. DC Electrical Specifications (continued)

Characteristic	Symbol	Min	Max	Unit
Input Capacitance <sup>2</sup> All input-only pins All input/output (three-state) pins	$C_{in}$	— —	7 7	pF
Core Operating Supply Current <sup>3</sup> Master Mode LIMP mode STOP mode Low Power mode	$I_{DD}$	—	170 TBD 1 TBD	mA mA mA mA

NOTES:

- <sup>1</sup> Refer to the signals section for pins having weak internal pull-up devices.
- <sup>2</sup> This parameter is characterized before qualification rather than 100% tested.
- <sup>3</sup> Current measured at maximum system clock frequency, all modules active, and default drive strength with matching load.

### 5.4.1 PLL Power Filtering

To further enhance noise isolation, an external filter is strongly recommended for PLL analog  $V_{DD}$  pins. The filter shown in Figure 11 should be connected between the board  $V_{DD}$  and the  $PLL V_{DD}$  pins. The resistor and capacitors should be placed as close to the dedicated  $PLL V_{DD}$  pin as possible.

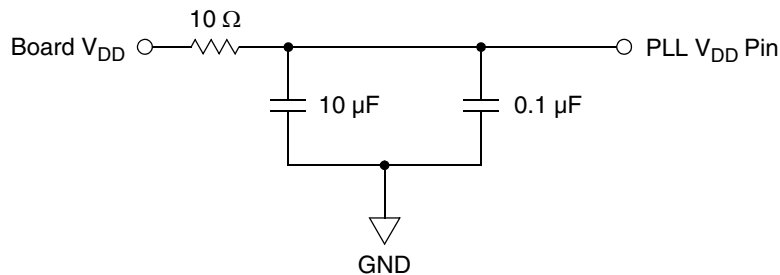
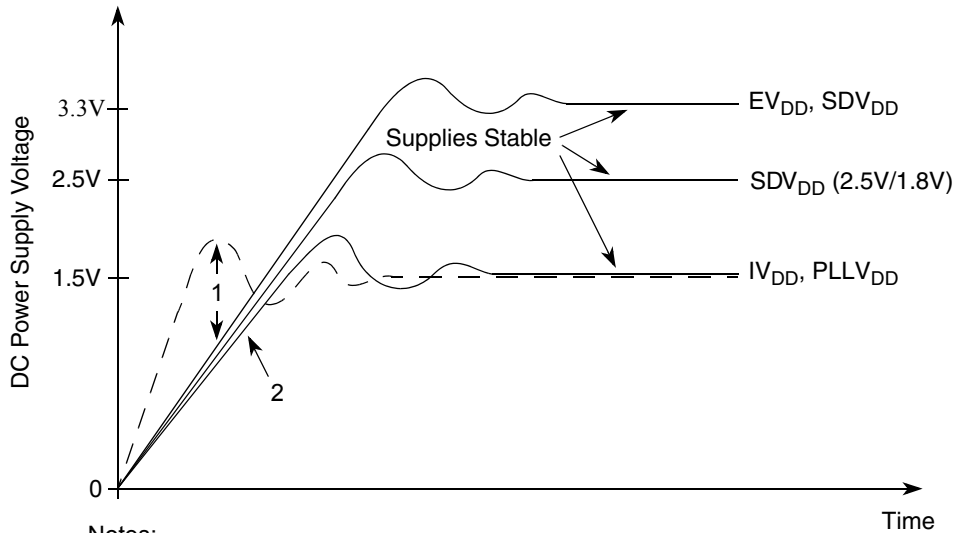


Figure 11. System  $PLL V_{DD}$  Power Filter

### 5.4.2 Supply Voltage Sequencing and Separation Cautions

Figure 12 shows situations in sequencing the I/O  $V_{DD}$  ( $EV_{DD}$ ), SDRAM  $V_{DD}$  ( $SDV_{DD}$ ),  $PLL V_{DD}$  ( $PLL V_{DD}$ ), and Core  $V_{DD}$  ( $IV_{DD}$ ).



## Notes:

1.  $IV_{DD}$  should not exceed  $EV_{DD}$ ,  $SDV_{DD}$  or  $PLL_{V_{DD}}$  by more than 0.4 V at any time, including power-up.
2. Recommended that  $IV_{DD}/PLL_{V_{DD}}$  should track  $EV_{DD}/SDV_{DD}$  up to 0.9 V, then separate for completion of ramps.
3. Input voltage must not be greater than the supply voltage ( $EV_{DD}$ ,  $SDV_{DD}$ ,  $IV_{DD}$ , or  $PLL_{V_{DD}}$ ) by more than 0.5 V at any time, including during power-up.
4. Use 1  $\mu$ s or slower rise time for all supplies.

**Figure 12. Supply Voltage Sequencing and Separation Cautions**

The relationship between  $SDV_{DD}$  and  $EV_{DD}$  is non-critical during power-up and power-down sequences. Both  $SDV_{DD}$  (2.5V or 3.3V) and  $EV_{DD}$  are specified relative to  $IV_{DD}$ .

### 5.4.2.1 Power Up Sequence

If  $EV_{DD}/SDV_{DD}$  are powered up with  $IV_{DD}$  at 0 V, then the sense circuits in the I/O pads will cause all pad output drivers connected to the  $EV_{DD}/SDV_{DD}$  to be in a high impedance state. There is no limit on how long after  $EV_{DD}/SDV_{DD}$  powers up before  $IV_{DD}$  must be powered up.  $IV_{DD}$  should not lead the  $EV_{DD}$ ,  $SDV_{DD}$  or  $PLL_{V_{DD}}$  by more than 0.4 V during power ramp-up, or there will be high current in the internal ESD protection diodes. The rise times on the power supplies should be slower than 1  $\mu$ s to avoid turning on the internal ESD protection clamp diodes.

The recommended power up sequence is as follows:

1. Use 1  $\mu$ s or slower rise time for all supplies.
2.  $IV_{DD}/PLL_{V_{DD}}$  and  $EV_{DD}/SDV_{DD}$  should track up to 0.9 V, then separate for the completion of ramps with  $EV_{DD}/SDV_{DD}$  going to the higher external voltages. One way to accomplish this is to use a low drop-out voltage regulator.

### 5.4.2.2 Power Down Sequence

If  $IV_{DD}/PLL_{V_{DD}}$  are powered down first, then sense circuits in the I/O pads will cause all output drivers to be in a high impedance state. There is no limit on how long after  $IV_{DD}$  and  $PLL_{V_{DD}}$  power down before  $EV_{DD}$  or  $SDV_{DD}$  must power down.  $IV_{DD}$  should not lag  $EV_{DD}$ ,  $SDV_{DD}$ , or  $PLL_{V_{DD}}$  going low by more

## Preliminary Electrical Characteristics

than 0.4 V during power down or there will be undesired high current in the ESD protection diodes. There are no requirements for the fall times of the power supplies.

The recommended power down sequence is as follows:

1. Drop  $IV_{DD}/PLL V_{DD}$  to 0 V.
2. Drop  $EV_{DD}/SDV_{DD}$  supplies.

## 5.5 Oscillator and PLL Electrical Characteristics

Table 8. PLL Electrical Characteristics

Num	Characteristic	Symbol	Min. Value	Max. Value	Unit
1	PLL Reference Frequency Range				
	Crystal reference	$f_{ref\_crystal}$	TBD	16	MHz
	External reference	$f_{ref\_ext}$	TBD	16	MHz
2	Core frequency	$f_{sys}$	TBD	166.67	MHz
	CLKOUT Frequency <sup>1</sup>	$f_{sys}/2$	TBD	83.33	MHz
3	Crystal Start-up Time <sup>2, 3</sup>	$t_{cst}$	—	10	ms
4	EXTAL Input High Voltage				
	Crystal Mode <sup>4</sup>	$V_{IHEXT}$	TBD	TBD	V
	All other modes (External, Limp)	$V_{IHEXT}$	TBD	TBD	V
5	EXTAL Input Low Voltage				
	Crystal Mode <sup>4</sup>	$V_{ILEXT}$	TBD	TBD	V
	All other modes (External, Limp)	$V_{ILEXT}$	TBD	TBD	V
6	XTAL Load Capacitance <sup>2</sup>		5	30	pF
11	PLL Lock Time <sup>2,5</sup>	$t_{pll}$	—	1	ms
14	Duty Cycle of reference <sup>2</sup>	$t_{dc}$	40	60	%

### NOTES:

<sup>1</sup> All internal registers retain data at 0 Hz.

<sup>2</sup> This parameter is guaranteed by characterization before qualification rather than 100% tested.

<sup>3</sup> Proper PC board layout procedures must be followed to achieve specifications.

<sup>4</sup> This parameter is guaranteed by design rather than 100% tested.

## 5.6 External Interface Timing Characteristics

Table 9 lists processor bus input timings.

### NOTE

All processor bus timings are synchronous; that is, input setup/hold and output delay with respect to the rising edge of a reference clock. The reference clock is the FB\_CLK output.

All other timing relationships can be derived from these values. Timings listed in Table 9 are shown in Figure 14 & Figure 15.



\* The timings are also valid for inputs sampled on the negative clock edge.

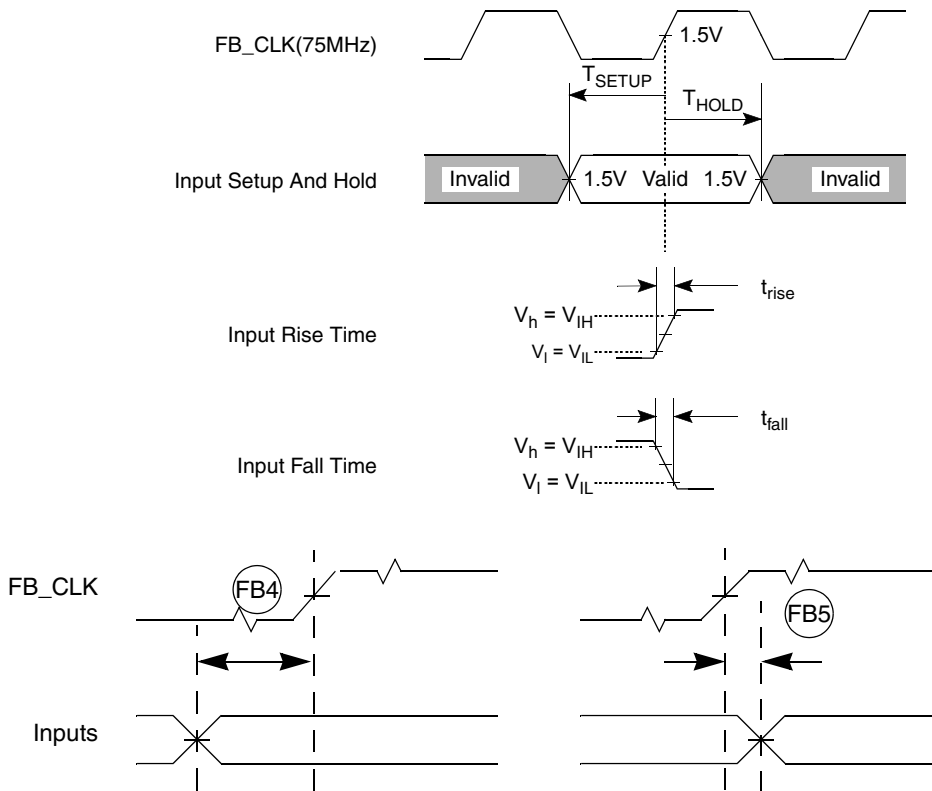


Figure 13. General Input Timing Requirements

## 5.6.1 FlexBus

A multi-function external bus interface called FlexBus is provided to interface to slave-only devices up to a maximum bus frequency of 83.33 MHz. It can be directly connected to asynchronous or synchronous devices such as external boot ROMs, Flash memories, gate-array logic, or other simple target (slave) devices with little or no additional circuitry. For asynchronous devices a simple chip-select based interface can be used. The FlexBus interface has six general purpose chip-selects ( $\overline{\text{FB\_CS}}[5:0]$ ) which can be configured to be distributed between the FlexBus or SDRAM memory interfaces. Chip-select  $\overline{\text{FB\_CS}}[0]$  can be dedicated to boot ROM access and can be programmed to be byte (8 bits), word (16 bits), or longword (32 bits) wide. Control signal timing is compatible with common ROM/Flash memories.

### 5.6.1.1 FlexBus AC Timing Characteristics

The following timing numbers indicate when data will be latched or driven onto the external bus, relative to the system clock.

Table 9. FlexBus AC Timing Specifications

Num	Characteristic	Symbol	Min	Max	Unit	Notes
	Frequency of Operation			83.33	Mhz	$f_{\text{sys}}/2$
FB1	Clock Period (FB_CLK)	$t_{\text{FBCK}}$		12	ns	$t_{\text{cyc}}$

Preliminary Electrical Characteristics

Table 9. FlexBus AC Timing Specifications

Num	Characteristic	Symbol	Min	Max	Unit	Notes
FB2	Data, and Control Output Valid (A[23:0], D[31:0], $\overline{\text{FB\_CS}}[5:0]$ , R/W, $\overline{\text{TS}}$ , $\overline{\text{BE/BWE}}[3:0]$ and $\overline{\text{OE}}$ )	$t_{\text{FBCHDCV}}$	—	7.0	ns	1
FB3	Data, and Control Output Hold ((A[23:0], D[31:0], $\overline{\text{FB\_CS}}[5:0]$ , R/W, $\overline{\text{TS}}$ , $\overline{\text{BE/BWE}}[3:0]$ , and $\overline{\text{OE}}$ )	$t_{\text{FBCHDCI}}$	1	—	ns	1, 2
FB4	Data Input Setup	$t_{\text{DVF BCH}}$	3.5	—	ns	
FB5	Data Input Hold	$t_{\text{DIF BCH}}$	0	—	ns	
FB6	Transfer Acknowledge ( $\overline{\text{TA}}$ ) Input Setup	$t_{\text{CV F B C H}}$	4	—	ns	
FB7	Transfer Acknowledge ( $\overline{\text{TA}}$ ) Input Hold	$t_{\text{CIF B C H}}$	0	—	ns	
FB8	Address Output Valid (A[23:0])	$t_{\text{FBCHAV}}$	—	6.0	ns	3
FB9	Address Output Hold (A[23:0])	$t_{\text{FBCHAI}}$	1.0	—	ns	

NOTES:

- Timing for chip selects only applies to the  $\overline{\text{FB\_CS}}[5:0]$  signals. Please see Section 5.7, "SDRAM BUS" for  $\overline{\text{SD\_CS}}[1:0]$  timing.
- The FlexBus supports programming an extension of the address hold. Please consult the device reference manual for more information.
- These specs are used when the A[23:0] signals are configured as 23-bit, non-muxed FlexBus address signals.

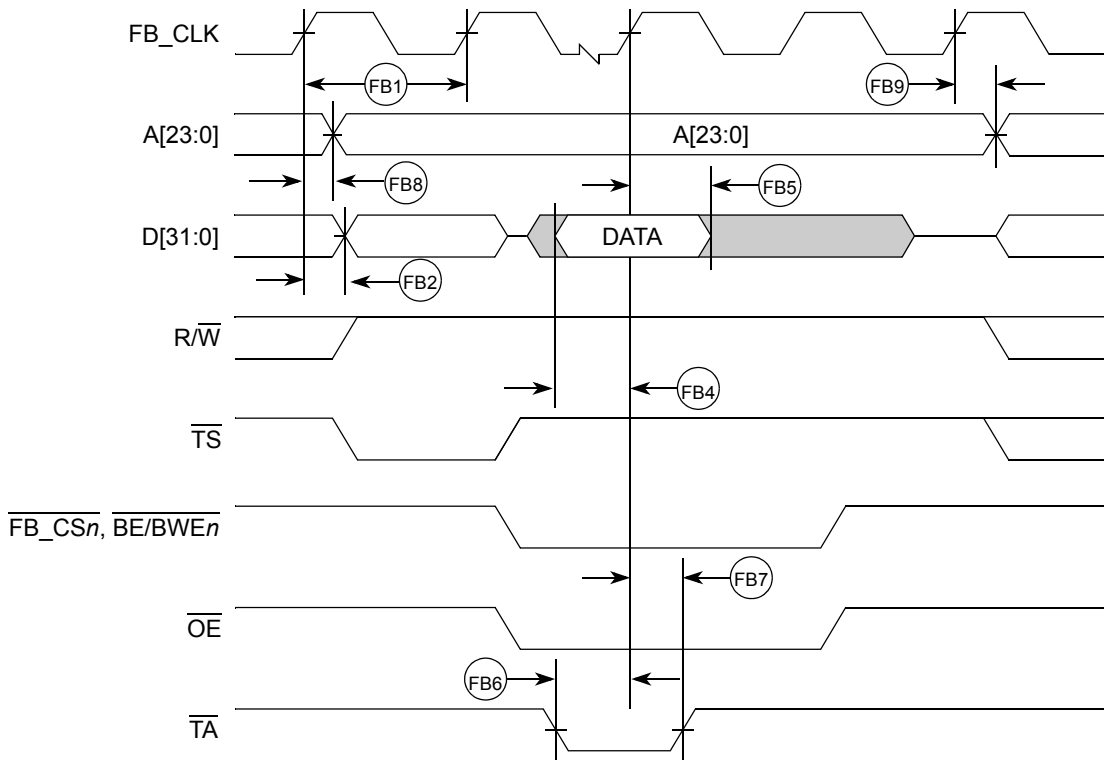


Figure 14. FlexBus Read Timing

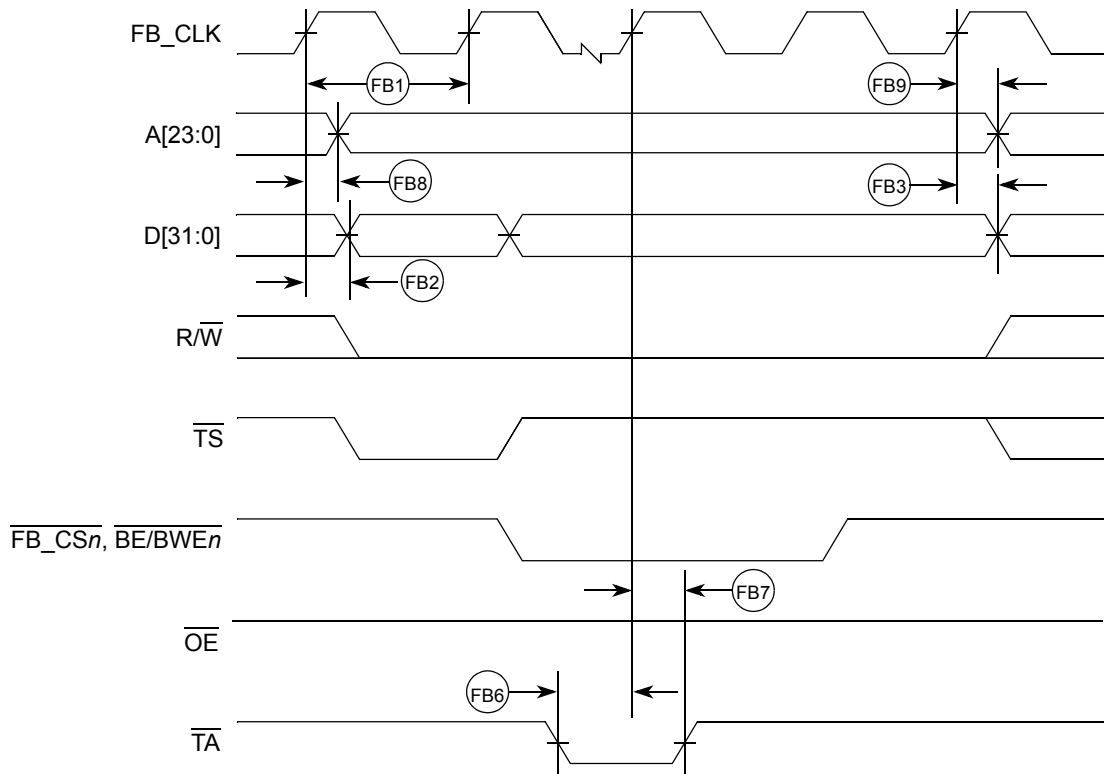


Figure 15. Flexbus Write Timing

## 5.7 SDRAM Bus

The SDRAM controller supports accesses to main SDRAM memory from any internal master. It supports either standard SDRAM or double data rate (DDR) SDRAM, but it does not support both at the same time. The SDRAM controller uses SSTL2 and SSTL3 I/O drivers. Both SSTL drive modes are programmable for either Class I or Class II drive strength.

### 5.7.1 SDR SDRAM AC Timing Characteristics

The following timing numbers indicate when data will be latched or driven onto the external bus, relative to the memory bus clock, when operating in SDR mode on write cycles and relative to SD\_DQS on read cycles. The SDRAM controller is a DDR controller that has an SDR mode. Because it is designed to support DDR, a DQS pulse must still be supplied to the device for each data beat of an SDR read. The ColdFire processor accomplishes this by asserting a signal called SD\_DQS during read cycles. Care must be taken during board design to adhere to the following guidelines and specs with regard to the SD\_DQS signal and its usage.

## Preliminary Electrical Characteristics

**Table 10. SDR Timing Specifications**

Symbol	Characteristic	Symbol	Min	Max	Unit	Notes
	Frequency of Operation		—	83.33	MHz	1
SD1	Clock Period ( $t_{CK}$ )	$t_{SDCK}$	7.52	12	ns	2
SD2	Clock Skew ( $t_{SK}$ )	$t_{SDSK}$	—	TBD		
SD3	Pulse Width High ( $t_{CKH}$ )	$t_{SDCKH}$	0.45	0.55	SD_CLK	3
SD4	Pulse Width Low ( $t_{CKL}$ )	$t_{SDCKL}$	0.45	0.55	SD_CLK	3
SD5	Address, $\overline{SD\_CKE}$ , $\overline{SD\_CAS}$ , $\overline{SD\_RAS}$ , $\overline{SD\_WE}$ , $\overline{SD\_BA}$ , $\overline{SD\_CS}[1:0]$ - Output Valid ( $t_{CMV}$ )	$t_{SDCHACV}$	—	$0.5 \times SD\_CLK + 1.0$	ns	
SD6	Address, $\overline{SD\_CKE}$ , $\overline{SD\_CAS}$ , $\overline{SD\_RAS}$ , $\overline{SD\_WE}$ , $\overline{SD\_BA}$ , $\overline{SD\_CS}[1:0]$ - Output Hold ( $t_{CMH}$ )	$t_{SDCHACI}$	2.0	—	ns	
SD7	$\overline{SD\_SDR\_DQS}$ Output Valid ( $t_{DQSOV}$ )	$t_{DQSOV}$	—	Self timed	ns	4
SD8	$\overline{SD\_DQS}[3:0]$ input setup relative to $\overline{SD\_CLK}$ ( $t_{DQSI S}$ )	$t_{DQVSDCH}$	$0.25 \times SD\_CLK$	$0.40 \times SD\_CLK$	ns	5
SD9	$\overline{SD\_DQS}[3:2]$ input hold relative to $\overline{SD\_CLK}$ ( $t_{DQSIH}$ )	$t_{DQISDCH}$	Does not apply. 0.5 SD_CLK fixed width.			6
SD10	Data (D[31:0]) Input Setup relative to $\overline{SD\_CLK}$ (reference only) ( $t_{DIS}$ )	$t_{DVSDCH}$	$0.25 \times SD\_CLK$	—	ns	7
SD11	Data Input Hold relative to $\overline{SD\_CLK}$ (reference only) ( $t_{DIH}$ )	$t_{DISDCH}$	1.0	—	ns	
SD12	Data (D[31:0]) and Data Mask( $\overline{SD\_DQM}[3:0]$ ) Output Valid ( $t_{DV}$ )	$t_{SDCHDMV}$	—	$0.75 \times SD\_CLK + 0.5$	ns	
SD13	Data (D[31:0]) and Data Mask ( $\overline{SD\_DQM}[3:0]$ ) Output Hold ( $t_{DH}$ )	$t_{SDCHDMI}$	1.5	—	ns	

**NOTES:**

- 1 The device supports the same frequency of operation for both FlexBus and SDRAM as that of the internal bus clock. Please see the PLL chapter of the *MCF5208 Reference Manual* for more information on setting the SDRAM clock rate.
- 2 SD\_CLK is one SDRAM clock in (ns).
- 3 Pulse width high plus pulse width low cannot exceed min and max clock period.
- 4 SD\_DQS is designed to pulse 0.25 clock before the rising edge of the memory clock. This is a guideline only. Subtle variation from this guideline is expected. SD\_DQS will only pulse during a read cycle and one pulse will occur for each data beat.
- 5 SDR\_DQS is designed to pulse 0.25 clock before the rising edge of the memory clock. This spec is a guideline only. Subtle variation from this guideline is expected. SDR\_DQS will only pulse during a read cycle and one pulse will occur for each data beat.
- 6 The SDR\_DQS pulse is designed to be 0.5 clock in width. The timing of the rising edge is most important. The falling edge does not affect the memory controller.
- 7 Since a read cycle in SDR mode still uses the DQS circuit within the device, it is most critical that the data valid window be centered 1/4 clk after the rising edge of DQS. Ensuring that this happens will result in successful SDR reads. The input setup spec is just provided as guidance.

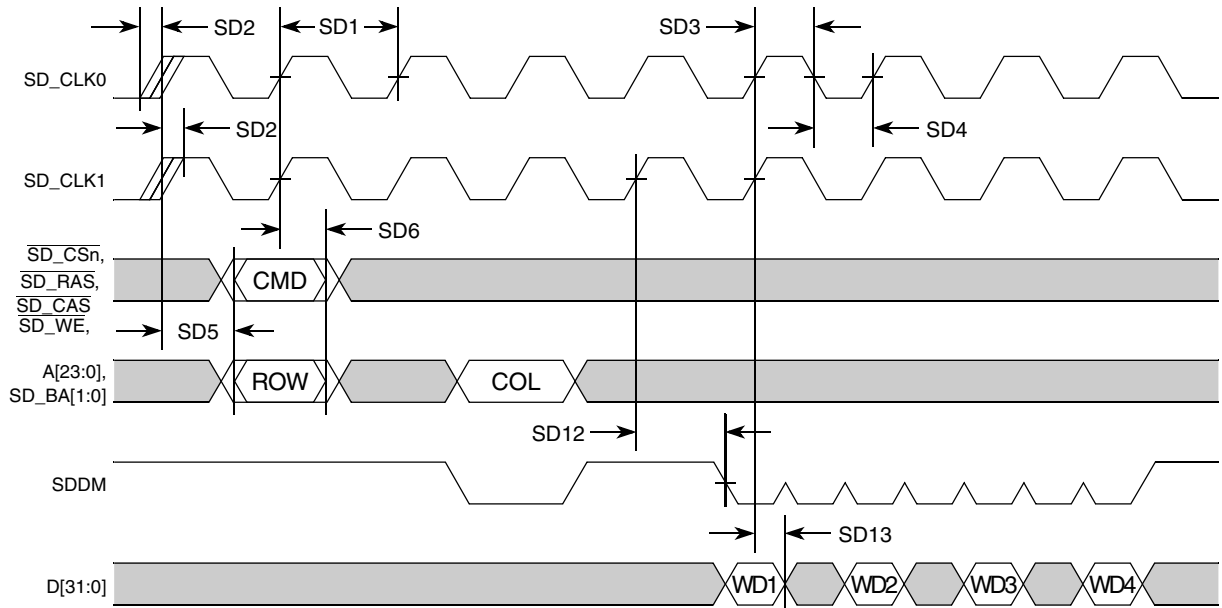
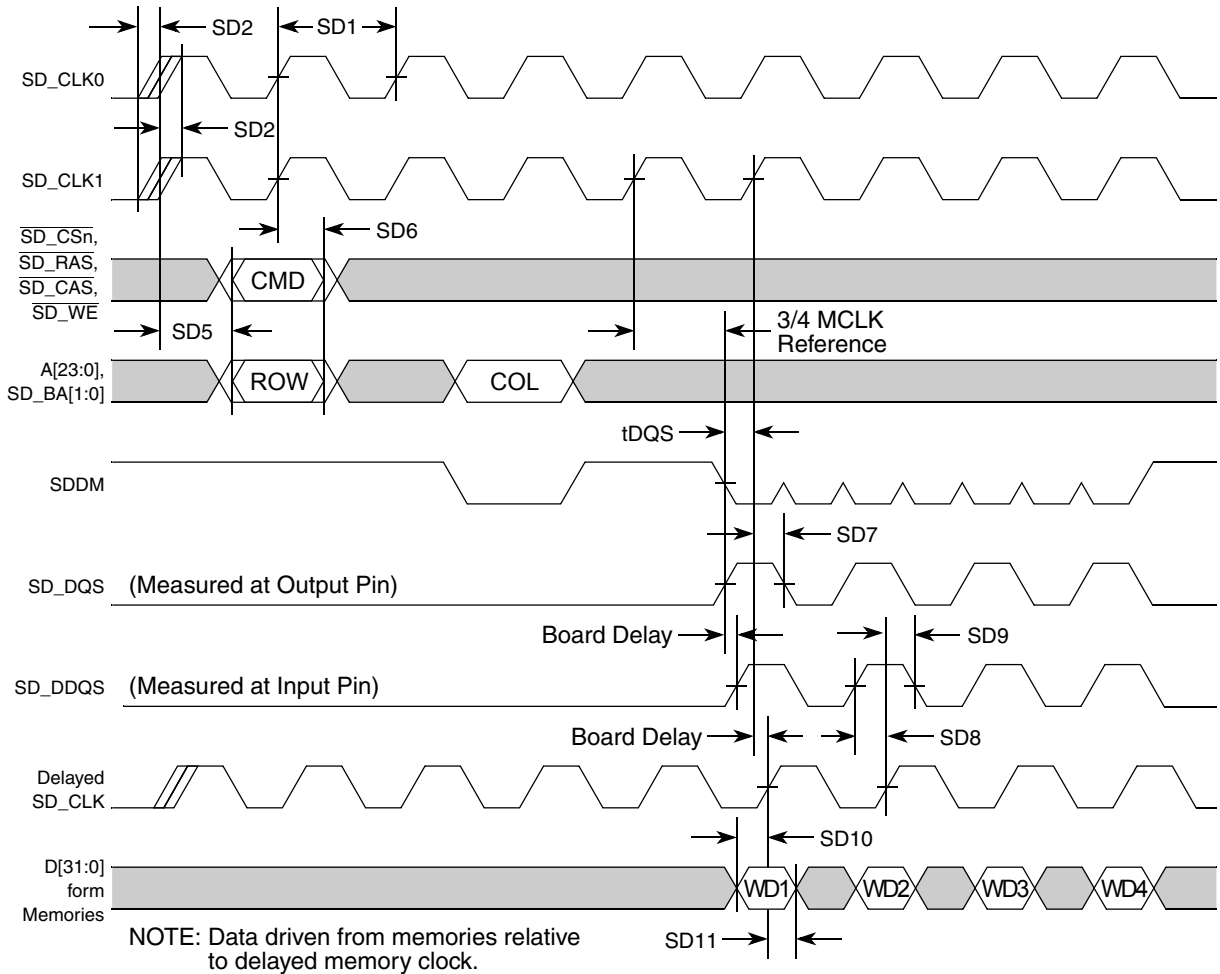


Figure 16. SDR Write Timing

**Preliminary Electrical Characteristics**



**Figure 17. SDR Read Timing**

**5.7.2 DDR SDRAM AC Timing Characteristics**

When using the SDRAM controller in DDR mode, the following timing numbers must be followed to properly latch or drive data onto the memory bus. All timing numbers are relative to the four DQS byte lanes. The following timing numbers are subject to change at anytime, and are only provided to aid in early board design. Please contact your local Freescale representative if questions develop.

**Table 11. DDR Timing Specifications**

Num	Characteristic	Symbol	Min	Max	Unit	Notes
	Frequency of Operation		83.33	TBD	Mhz	1
DD1	Clock Period (SD_CLK)	$t_{DDCK}$	TBD	12	ns	2
DD2	Pulse Width High	$t_{DDCKH}$	0.45	0.55	SD_CLK	3
DD3	Pulse Width Low	$t_{DDCKL}$	0.45	0.55	SD_CLK	3
DD4	Address, $\overline{SD\_CKE}$ , $\overline{SD\_CAS}$ , $\overline{SD\_RAS}$ , $\overline{SD\_WE}$ , $\overline{SD\_CS}[1:0]$ - Output Valid	$t_{SDCHACV}$	—	$0.5 \times SD\_CLK + 1.0$	ns	4

Table 11. DDR Timing Specifications (continued)

Num	Characteristic	Symbol	Min	Max	Unit	Notes
DD5	Address, SD_CKE, $\overline{\text{SD\_CAS}}$ , $\overline{\text{SD\_RAS}}$ , $\overline{\text{SD\_WE}}$ , $\overline{\text{SD\_CS}}[1:0]$ - Output Hold	$t_{\text{SDCHACI}}$	2.0	—	ns	
DD6	Write Command to first DQS Latching Transition	$t_{\text{CMDVDQ}}$		1.25	SD_CLK	
DD7	Data and Data Mask Output Setup (DQ-->DQS) Relative to DQS (DDR Write Mode)	$t_{\text{DQDMV}}$	1.5	—	ns	5 6
DD8	Data and Data Mask Output Hold (DQS-->DQ) Relative to DQS (DDR Write Mode)	$t_{\text{DQDMI}}$	1.0	—	ns	7
DD9	Input Data Skew Relative to DQS (Input Setup)	$t_{\text{DVDQ}}$	—	1	ns	8
DD10	Input Data Hold Relative to DQS.	$t_{\text{DIDQ}}$	$0.25 \times \text{SD\_CLK} + 0.5\text{ns}$	—	ns	9
DD11	DQS falling edge from SDCLK rising (output hold time)	$t_{\text{DQLSDCH}}$	0.5	—	ns	
DD12	DQS input read preamble width ( $t_{\text{RPRE}}$ )	$t_{\text{DQRPRE}}$	0.9	1.1	SD_CLK	
DD13	DQS input read postamble width ( $t_{\text{RPST}}$ )	$t_{\text{DQRPST}}$	0.4	0.6	SD_CLK	
DD14	DQS output write preamble width ( $t_{\text{WPRE}}$ )	$t_{\text{DQWPRE}}$	0.25	—	SD_CLK	
DD15	DQS output write postamble width ( $t_{\text{WPST}}$ )	$t_{\text{DQWPST}}$	0.4	0.6	SD_CLK	

## NOTES:

- <sup>1</sup> The frequency of operation is either 2x or 4x the FB\_CLK frequency of operation. FlexBus and SDRAM clock operate at the same frequency as the internal bus clock.
- <sup>2</sup> SD\_CLK is one SDRAM clock in (ns).
- <sup>3</sup> Pulse width high plus pulse width low cannot exceed min and max clock period.
- <sup>4</sup> Command output valid should be 1/2 the memory bus clock (SD\_CLK) plus some minor adjustments for process, temperature, and voltage variations.
- <sup>5</sup> This specification relates to the required input setup time of today's DDR memories. The device's output setup should be larger than the input setup of the DDR memories. If it is not larger, then the input setup on the memory will be in violation. MEM\_DATA[31:24] is relative to MEM\_DQS[3], MEM\_DATA[23:16] is relative to MEM\_DQS[2], MEM\_DATA[15:8] is relative to MEM\_DQS[1], and MEM\_[7:0] is relative MEM\_DQS[0].
- <sup>6</sup> The first data beat will be valid before the first rising edge of DQS and after the DQS write preamble. The remaining data beats will be valid for each subsequent DQS edge.
- <sup>7</sup> This specification relates to the required hold time of today's DDR memories. MEM\_DATA[31:24] is relative to MEM\_DQS[3], MEM\_DATA[23:16] is relative to MEM\_DQS[2], MEM\_DATA[15:8] is relative to MEM\_DQS[1], and MEM\_[7:0] is relative MEM\_DQS[0].
- <sup>8</sup> Data input skew is derived from each DQS clock edge. It begins with a DQS transition and ends when the last data line becomes valid. This input skew must include DDR memory output skew and system level board skew (due to routing or other factors).
- <sup>9</sup> Data input hold is derived from each DQS clock edge. It begins with a DQS transition and ends when the first data line becomes invalid.

Preliminary Electrical Characteristics

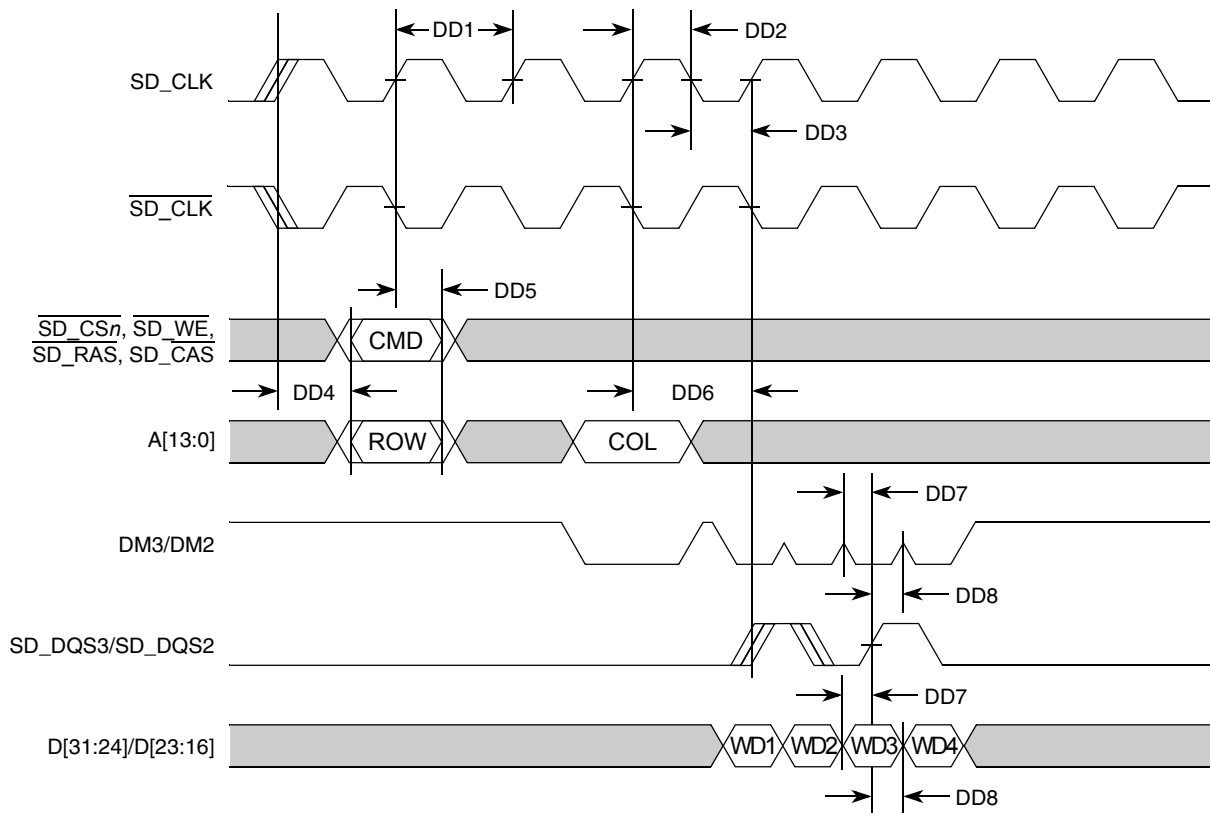


Figure 18. DDR Write Timing



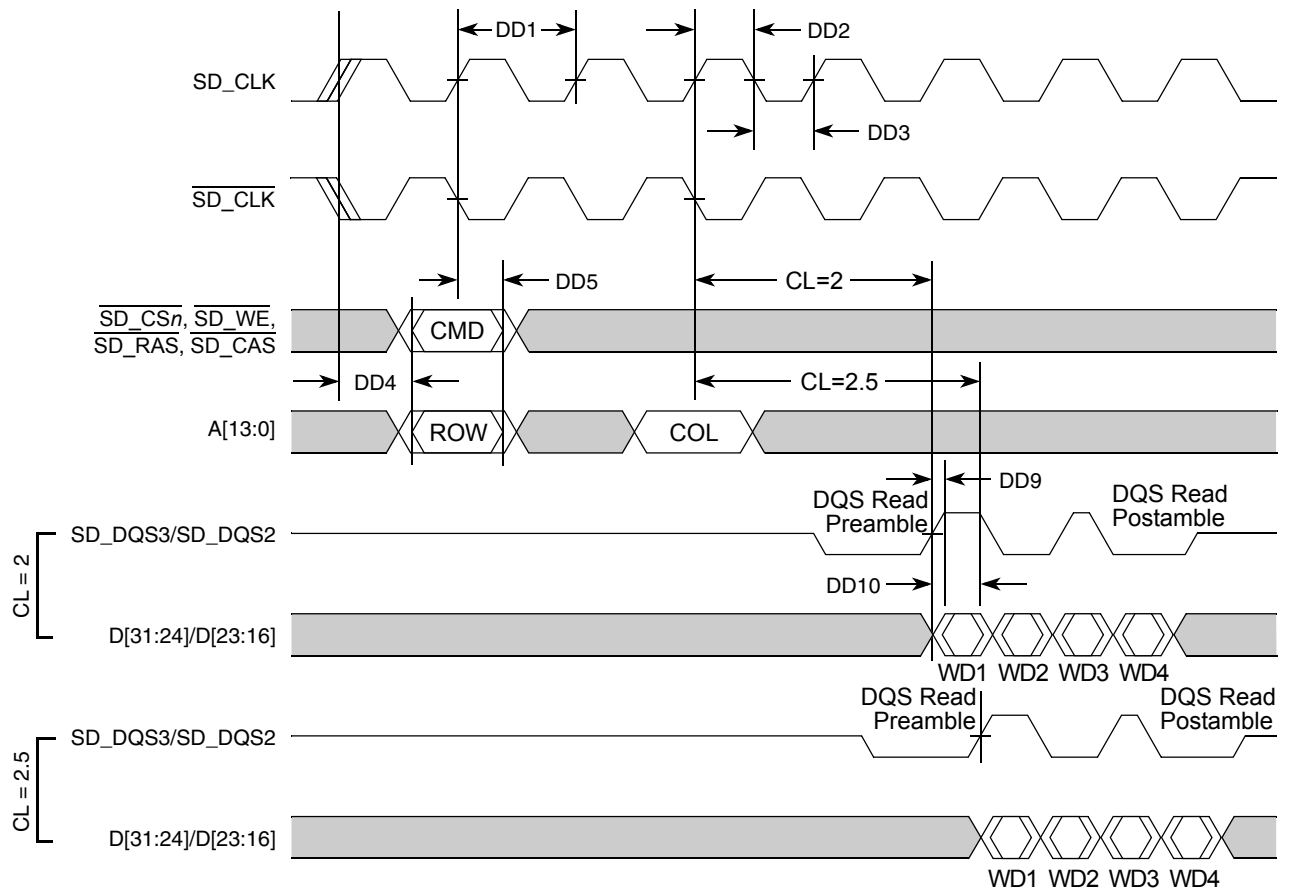


Figure 19. DDR Read Timing

Figure 20 shows the DDR clock crossover specifications.

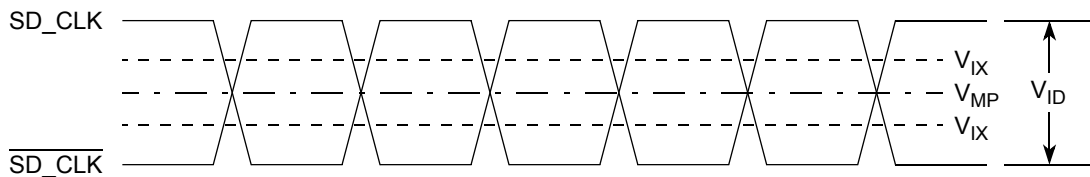


Figure 20. DDR Clock Crossover Timing

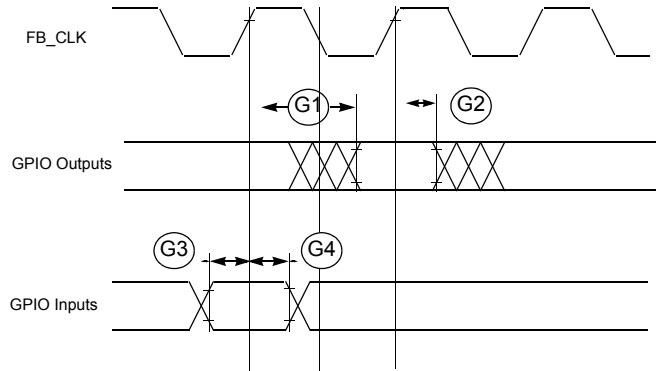
## 5.8 General Purpose I/O Timing

Table 12. GPIO Timing<sup>1</sup>

Num	Characteristic	Symbol	Min	Max	Unit
G1	FB_CLK High to GPIO Output Valid	$t_{CHPOV}$	—	8	ns
G2	FB_CLK High to GPIO Output Invalid	$t_{CHPOI}$	1.5	—	ns
G3	GPIO Input Valid to FB_CLK High	$t_{PVCH}$	8	—	ns
G4	FB_CLK High to GPIO Input Invalid	$t_{CHPI}$	1.5	—	ns

**Preliminary Electrical Characteristics**

NOTES:  
<sup>1</sup> GPIO spec cover:  $\overline{IRQn}$ , UART and Timer pins.



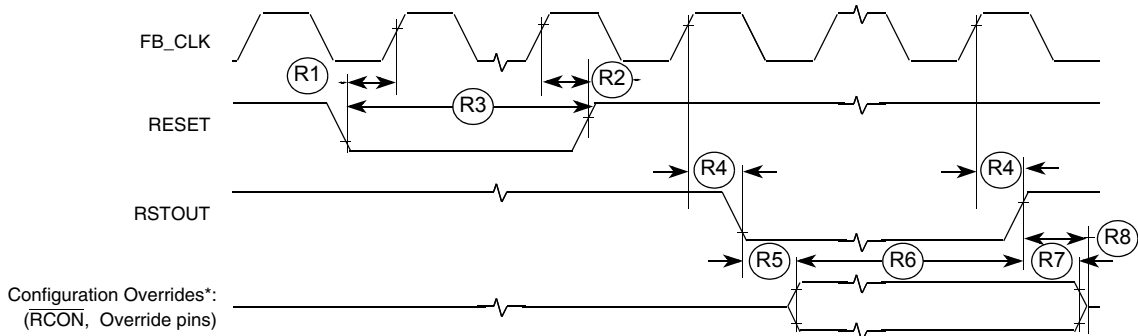
**Figure 21. GPIO Timing**

## 5.9 Reset and Configuration Override Timing

**Table 13. Reset and Configuration Override Timing**

Num	Characteristic	Symbol	Min	Max	Unit
R1	$\overline{RESET}$ Input valid to FB_CLK High	$t_{RVCH}$	9	—	ns
R2	FB_CLK High to $\overline{RESET}$ Input invalid	$t_{CHRI}$	1.5	—	ns
R3	$\overline{RESET}$ Input valid Time <sup>1</sup>	$t_{RIVT}$	5	—	$t_{CYC}$
R4	FB_CLK High to $\overline{RSTOUT}$ Valid	$t_{CHROV}$	—	10	ns
R5	$\overline{RSTOUT}$ valid to Config. Overrides valid	$t_{ROVCV}$	0	—	ns
R6	Configuration Override Setup Time to $\overline{RSTOUT}$ invalid	$t_{COS}$	20	—	$t_{CYC}$
R7	Configuration Override Hold Time after $\overline{RSTOUT}$ invalid	$t_{COH}$	0	—	ns
R8	$\overline{RSTOUT}$ invalid to Configuration Override High Impedance	$t_{ROICZ}$	—	1	$t_{CYC}$

NOTES:  
<sup>1</sup> During low power STOP, the synchronizers for the  $\overline{RESET}$  input are bypassed and  $\overline{RESET}$  is asserted asynchronously to the system. Thus,  $\overline{RESET}$  must be held a minimum of 100 ns.



**Figure 22.  $\overline{RESET}$  and Configuration Override Timing**

**NOTE**

Refer to the *MCF5208 Reference Manual* for more information.

## 5.10 I<sup>2</sup>C Input/Output Timing Specifications

Table 14 and Table 15 list specifications for the I<sup>2</sup>C input and output timing parameters.

**Table 14. I<sup>2</sup>C Input Timing Specifications between I2C\_SCL and I2C\_SDA**

Num	Characteristic	Min	Max	Units
11	Start condition hold time	2	—	t <sub>cyc</sub>
12	Clock low period	8	—	t <sub>cyc</sub>
13	I2C_SCL/I2C_SDA rise time (V <sub>IL</sub> = 0.5 V to V <sub>IH</sub> = 2.4 V)	—	1	ms
14	Data hold time	0	—	ns
15	I2C_SCL/I2C_SDA fall time (V <sub>IH</sub> = 2.4 V to V <sub>IL</sub> = 0.5 V)	—	1	ms
16	Clock high time	4	—	t <sub>cyc</sub>
17	Data setup time	0	—	ns
18	Start condition setup time (for repeated start condition only)	2	—	t <sub>cyc</sub>
19	Stop condition setup time	2	—	t <sub>cyc</sub>

**Table 15. I<sup>2</sup>C Output Timing Specifications between I2C\_SCL and I2C\_SDA**

Num	Characteristic	Min	Max	Units
11 <sup>1</sup>	Start condition hold time	6	—	t <sub>cyc</sub>
12 <sup>1</sup>	Clock low period	10	—	t <sub>cyc</sub>
13 <sup>2</sup>	I2C_SCL/I2C_SDA rise time (V <sub>IL</sub> = 0.5 V to V <sub>IH</sub> = 2.4 V)	—	—	μs
14 <sup>1</sup>	Data hold time	7	—	t <sub>cyc</sub>
15 <sup>3</sup>	I2C_SCL/I2C_SDA fall time (V <sub>IH</sub> = 2.4 V to V <sub>IL</sub> = 0.5 V)	—	3	ns
16 <sup>1</sup>	Clock high time	10	—	t <sub>cyc</sub>
17 <sup>1</sup>	Data setup time	2	—	t <sub>cyc</sub>
18 <sup>1</sup>	Start condition setup time (for repeated start condition only)	20	—	t <sub>cyc</sub>
19 <sup>1</sup>	Stop condition setup time	10	—	t <sub>cyc</sub>

**NOTES:**

- <sup>1</sup> Note: Output numbers depend on the value programmed into the IFDR; an IFDR programmed with the maximum frequency (IFDR = 0x20) results in minimum output timings as shown in Table A-16. The I<sup>2</sup>C interface is designed to scale the actual data transition time to move it to the middle of the I2C\_SCL low period. The actual position is affected by the prescale and division values programmed into the IFDR; however, the numbers given in Table A-16 are minimum values.
- <sup>2</sup> Because I2C\_SCL and I2C\_SDA are open-collector-type outputs, which the processor can only actively drive low, the time I2C\_SCL or I2C\_SDA take to reach a high level depends on external signal capacitance and pull-up resistor values.
- <sup>3</sup> Specified at a nominal 50-pF load.

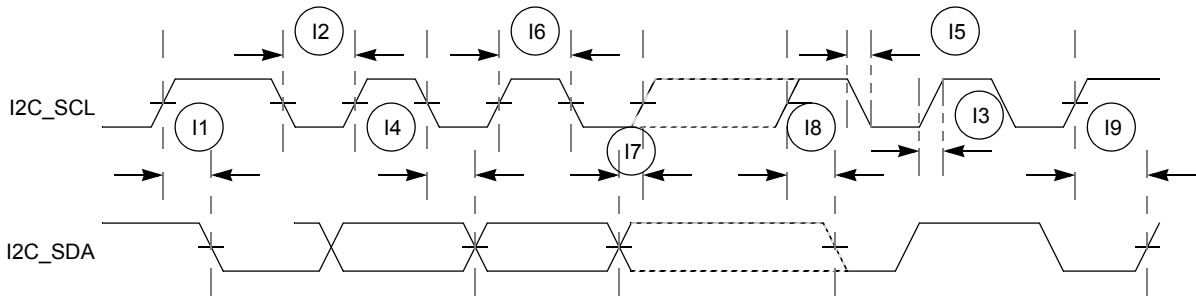


Figure 23. I<sup>2</sup>C Input/Output Timings

## 5.11 Fast Ethernet AC Timing Specifications

MII signals use TTL signal levels compatible with devices operating at either 5.0 V or 3.3 V.

### 5.11.1 MII Receive Signal Timing (FEC\_RXD[3:0], FEC\_RXDV, FEC\_RXER, and FEC\_RXCLK)

The receiver functions correctly up to a FEC\_RXCLK maximum frequency of 25 MHz +1%. There is no minimum frequency requirement. In addition, the processor clock frequency must exceed twice the FEC\_RXCLK frequency.

Table 16 lists MII receive channel timings.

Table 16. MII Receive Signal Timing

Num	Characteristic	Min	Max	Unit
M1	FEC_RXD[3:0], FEC_RXDV, FEC_RXER to FEC_RXCLK setup	5	—	ns
M2	FEC_RXCLK to FEC_RXD[3:0], FEC_RXDV, FEC_RXER hold	5	—	ns
M3	FEC_RXCLK pulse width high	35%	65%	FEC_RXCLK period
M4	FEC_RXCLK pulse width low	35%	65%	FEC_RXCLK period

Figure 24 shows MII receive signal timings listed in Table 16.

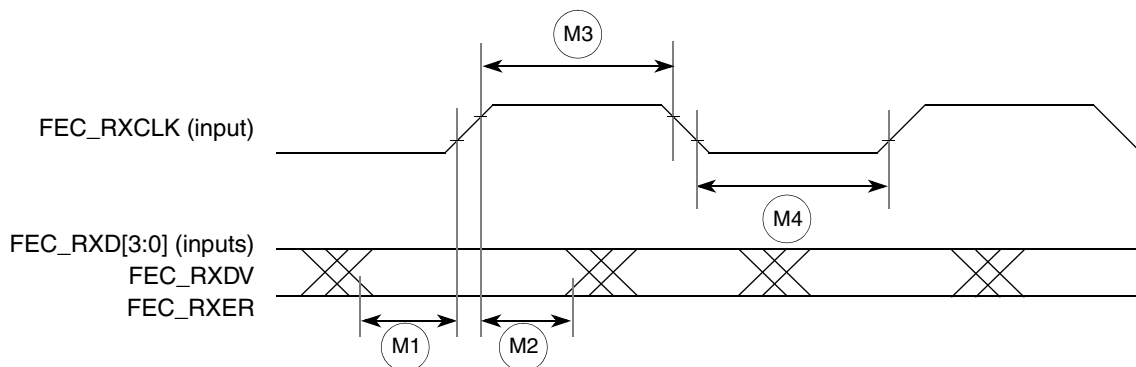


Figure 24. MII Receive Signal Timing Diagram

### 5.11.2 MII Transmit Signal Timing (FEC\_TXD[3:0], FEC\_TXEN, FEC\_TXER, FEC\_TXCLK)

Table 17 lists MII transmit channel timings.

The transmitter functions correctly up to a FEC\_TXCLK maximum frequency of 25 MHz +1%. There is no minimum frequency requirement. In addition, the processor clock frequency must exceed twice the FEC\_TXCLK frequency.

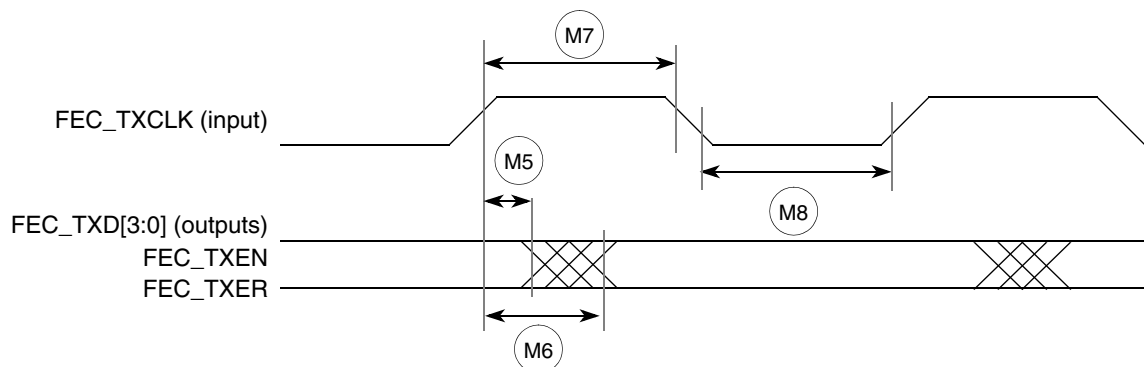
The transmit outputs (FEC\_TXD[3:0], FEC\_TXEN, FEC\_TXER) can be programmed to transition from either the rising or falling edge of FEC\_TXCLK, and the timing is the same in either case. This options allows the use of non-compliant MII PHYs.

Refer to the Ethernet chapter for details of this option and how to enable it.

**Table 17. MII Transmit Signal Timing**

Num	Characteristic	Min	Max	Unit
M5	FEC_TXCLK to FEC_TXD[3:0], FEC_TXEN, FEC_TXER invalid	5	—	ns
M6	FEC_TXCLK to FEC_TXD[3:0], FEC_TXEN, FEC_TXER valid	—	25	ns
M7	FEC_TXCLK pulse width high	35%	65%	FEC_TXCLK period
M8	FEC_TXCLK pulse width low	35%	65%	FEC_TXCLK period

Figure 25 shows MII transmit signal timings listed in Table 17.



**Figure 25. MII Transmit Signal Timing Diagram**

### 5.11.3 MII Async Inputs Signal Timing (FEC\_CRIS and FEC\_COL)

Table 18 lists MII asynchronous inputs signal timing.

**Table 18. MII Async Inputs Signal Timing**

Num	Characteristic	Min	Max	Unit
M9	FEC_CRIS, FEC_COL minimum pulse width	1.5	—	FEC_TXCLK period

Figure 26 shows MII asynchronous input timings listed in Table 18.

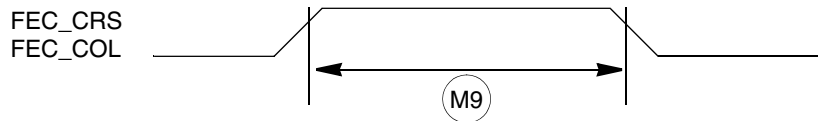


Figure 26. MII Async Inputs Timing Diagram

### 5.11.4 MII Serial Management Channel Timing (FEC\_MDIO and FEC\_MDC)

Table 19 lists MII serial management channel timings. The FEC functions correctly with a maximum MDC frequency of 2.5 MHz.

Table 19. MII Serial Management Channel Timing

Num	Characteristic	Min	Max	Unit
M10	FEC_MDC falling edge to FEC_MDIO output invalid (minimum propagation delay)	0	—	ns
M11	FEC_MDC falling edge to FEC_MDIO output valid (max prop delay)	—	25	ns
M12	FEC_MDIO (input) to FEC_MDC rising edge setup	10	—	ns
M13	FEC_MDIO (input) to FEC_MDC rising edge hold	0	—	ns
M14	FEC_MDC pulse width high	40%	60%	FEC_MDC period
M15	FEC_MDC pulse width low	40%	60%	FEC_MDC period

Figure 27 shows MII serial management channel timings listed in Table 19.

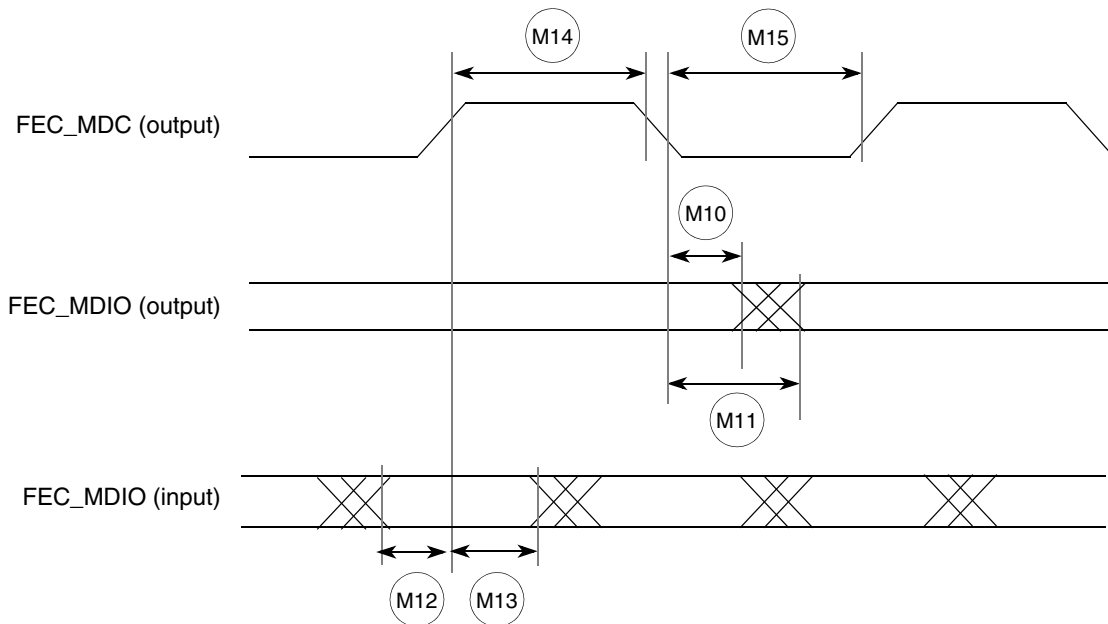


Figure 27. MII Serial Management Channel Timing Diagram

## 5.12 32-Bit Timer Module AC Timing Specifications

Table 20 lists timer module AC timings.

Table 20. Timer Module AC Timing Specifications

Name	Characteristic			Unit
		Min	Max	
T1	DT0IN / DT1IN / DT2IN / DT3IN cycle time	3	—	t <sub>CYC</sub>
T2	DT0IN / DT1IN / DT2IN / DT3IN pulse width	1	—	t <sub>CYC</sub>

## 5.13 QSPI Electrical Specifications

Table 21 lists QSPI timings.

Table 21. QSPI Modules AC Timing Specifications

Name	Characteristic	Min	Max	Unit
QS1	QSPI_CS[3:0] to QSPI_CLK	1	510	tcyc
QS2	QSPI_CLK high to QSPI_DOUT valid.	—	10	ns
QS3	QSPI_CLK high to QSPI_DOUT invalid. (Output hold)	1.5	—	ns
QS4	QSPI_DIN to QSPI_CLK (Input setup)	9	—	ns
QS5	QSPI_DIN to QSPI_CLK (Input hold)	9	—	ns

The values in Table 21 correspond to Figure 28.

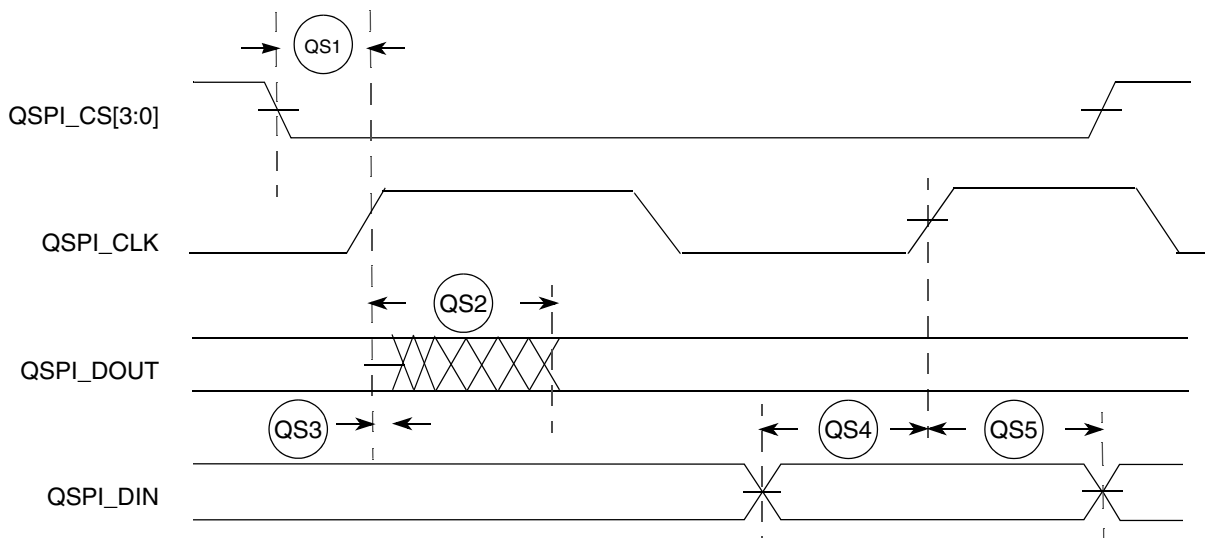


Figure 28. QSPI Timing

## 5.14 JTAG and Boundary Scan Timing

Table 22. JTAG and Boundary Scan Timing

Num	Characteristics <sup>1</sup>	Symbol	Min	Max	Unit
J1	TCLK Frequency of Operation	$f_{JCYC}$	DC	1/4	$f_{sys}/2$
J2	TCLK Cycle Period	$t_{JCYC}$	4	—	$t_{CYC}$
J3	TCLK Clock Pulse Width	$t_{JCW}$	26	—	ns
J4	TCLK Rise and Fall Times	$t_{JCRF}$	0	3	ns
J5	Boundary Scan Input Data Setup Time to TCLK Rise	$t_{BSDST}$	4	—	ns
J6	Boundary Scan Input Data Hold Time after TCLK Rise	$t_{BSDHT}$	26	—	ns
J7	TCLK Low to Boundary Scan Output Data Valid	$t_{BSDV}$	0	33	ns
J8	TCLK Low to Boundary Scan Output High Z	$t_{BSDZ}$	0	33	ns
J9	TMS, TDI Input Data Setup Time to TCLK Rise	$t_{TAPBST}$	4	—	ns
J10	TMS, TDI Input Data Hold Time after TCLK Rise	$t_{TAPBHT}$	10	—	ns
J11	TCLK Low to TDO Data Valid	$t_{TDODV}$	0	26	ns
J12	TCLK Low to TDO High Z	$t_{TDODZ}$	0	8	ns
J13	$\overline{TRST}$ Assert Time	$t_{TRSTAT}$	100	—	ns
J14	$\overline{TRST}$ Setup Time (Negation) to TCLK High	$t_{TRSTST}$	10	—	ns

NOTES:

<sup>1</sup> JTAG\_EN is expected to be a static signal. Hence, specific timing is not associated with it.

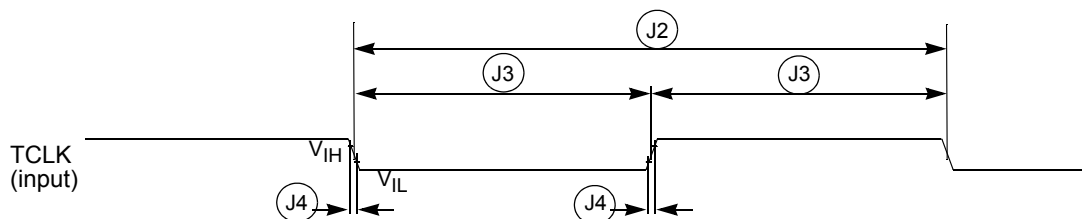


Figure 29. Test Clock Input Timing



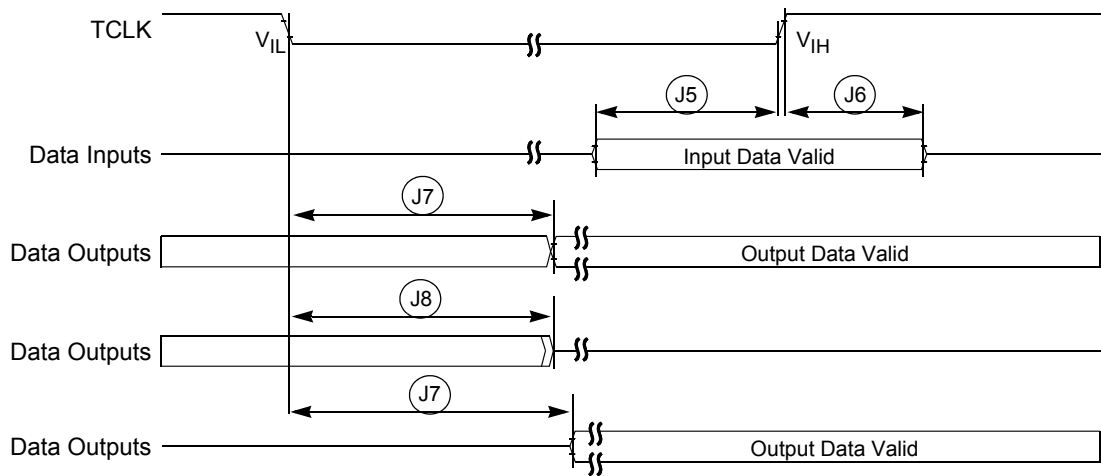


Figure 30. Boundary Scan (JTAG) Timing

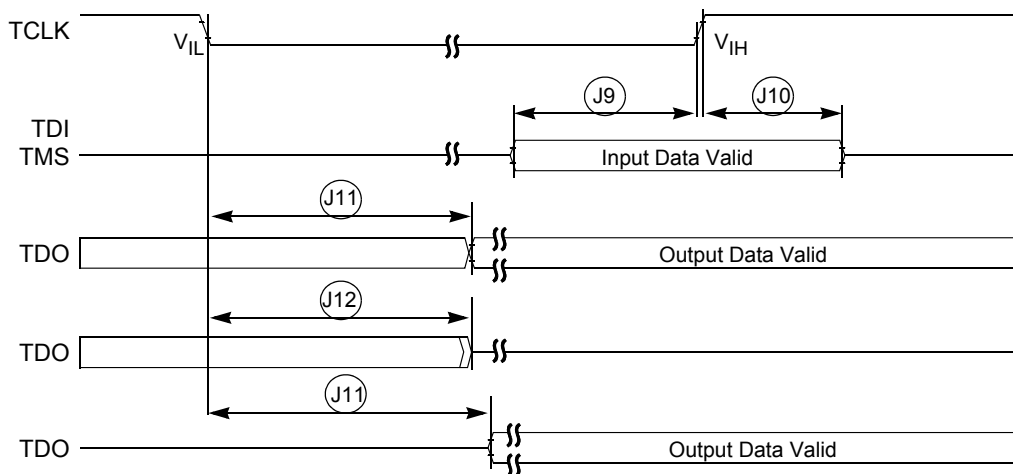


Figure 31. Test Access Port Timing

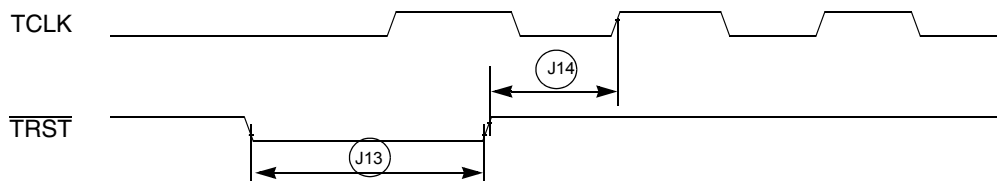


Figure 32.  $\overline{TRST}$  Timing

## 5.15 Debug AC Timing Specifications

Table 23 lists specifications for the debug AC timing parameters shown in Figure 33 & Figure 34.

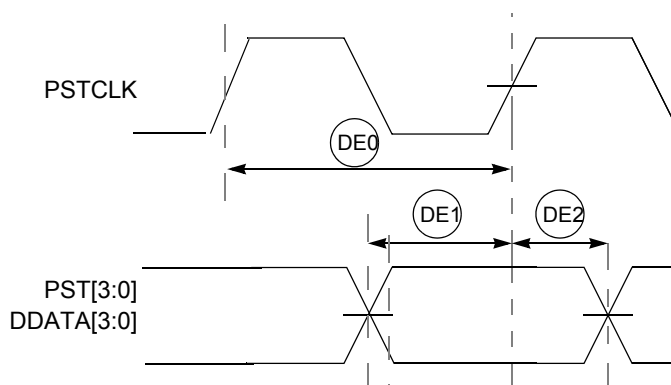
**Table 23. Debug AC Timing Specification**

Num	Characteristic			Units
		Min	Max	
DE0	PSTCLK cycle time	—	0.5	$t_{cyc}$
DE1	PST valid to PSTCLK high	2	—	ns
DE2	PSTCLK high to PST invalid	1	—	ns
DE3	DSCLK cycle time	5	—	$t_{cyc}$
DE4	DSI valid to DSCLK high	1	—	$t_{cyc}$
DE5 <sup>1</sup>	DSCLK high to DSO invalid	4	—	$t_{cyc}$
DE6	$\overline{BKPT}$ input data setup time to FB_CLK high	4	—	ns
DE7	FB_CLK high to $\overline{BKPT}$ invalid	0	—	ns

NOTES:

<sup>1</sup> DSCLK and DSI are synchronized internally. DE4 is measured from the synchronized DSCLK input relative to the rising edge of FB\_CLK.

Figure 33 shows real-time trace timing for the values in Table 23.



**Figure 33. Real-Time Trace AC Timing**

Figure 34 shows BDM serial port AC timing and  $\overline{BKPT}$  pin timing for the values in Table 23.

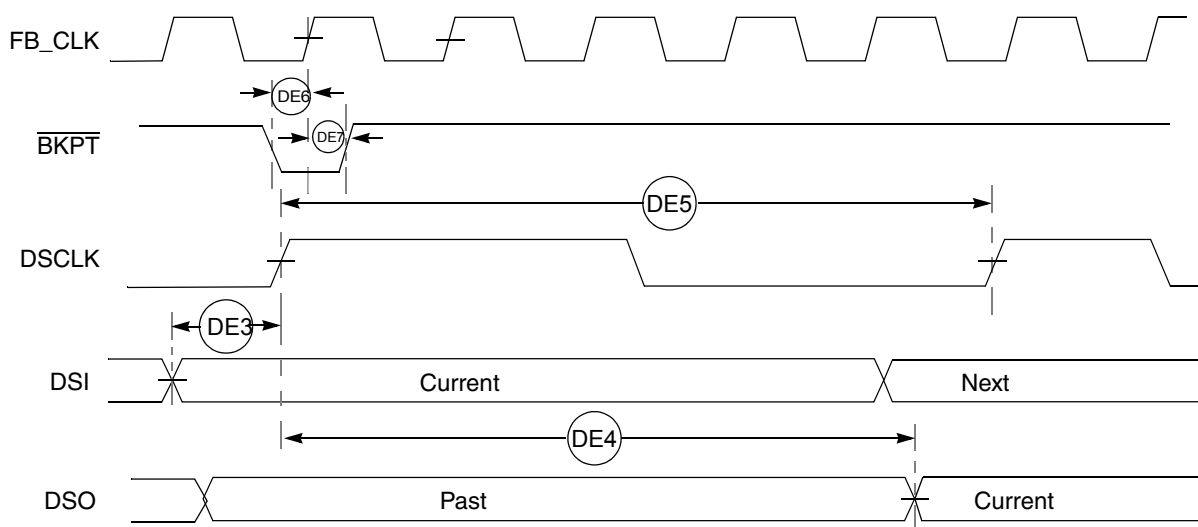


Figure 34. BDM Serial Port AC Timing

## 6 Revision History

Table 24. Revision History

Revision Number	Date	Substantive Changes
0	5/23/2005	<ul style="list-style-type: none"> <li>Initial Release</li> </ul>
0.1	6/16/2005	<ul style="list-style-type: none"> <li>Corrected 144QFP pinout in <a href="#">Figure 1</a>. Pins 139-142 incorrectly showed FEC functionality, which are actually UART 0/1 clear-to-send and request-to-send signals.</li> <li>Changed maximum core frequency in <a href="#">Table 8</a>, spec #2, from 240MHz to 166.67MHz. Also, changed symbols in table: <math>f_{core}</math> -&gt; <math>f_{sys}</math> and <math>f_{sys}</math> -&gt; <math>f_{sys}/2</math> for consistency throughout document and reference manual.</li> </ul>

## Revision History

**Table 24. Revision History (continued)**

Revision Number	Date	Substantive Changes
0.2	8/26/2005	<ul style="list-style-type: none"> <li>Changed ball M9 from SD_VDD to EVDD in <a href="#">Figure 9</a>.</li> <li><a href="#">Table 3</a>: Pin 33 for 144 LQFP package should be EVDD instead of SD_VDD. BE/BWE[3:0] for 144 LQFP should be “20, 48, 18, 50” instead of “18, 20, 48, 50”</li> </ul> <p>Cleaned up various electrical specifications:</p> <ul style="list-style-type: none"> <li><a href="#">Table 4</a>: Added DDR/Memory pad supply voltage spec, changed “clock synthesizer supply voltage” to “PLL supply voltage”, changed min PLLV<sub>DD</sub> from -0.5 to -0.3, changed max V<sub>IN</sub> from 4.0 to 3.6, changed minimum T<sub>stg</sub> from -65 to -55,</li> <li><a href="#">Table 5</a>: Changed TBD values in T<sub>j</sub> entry to 105°C.</li> <li><a href="#">Table 7</a>: Changed minimum core supply voltage from 1.35 to 1.4 and maximum from 1.65 to 1.6, added PLL supply voltage entry, added pad supply entries for mobile-DDR, DDR, and SDR, changed minimum input high voltage from 0.7xEV<sub>DD</sub> to 2 and maximum from 3.65 to EV<sub>DD</sub>+0.05, changed minimum input low voltage from VSS-0.3 to -0.05 and maximum from 0.35xEV<sub>DD</sub> to 0.8, added input high/low voltage entries for DDR and mobile-DDR, removed high impedance leakage current entry, changed minimum output high voltage from EV<sub>DD</sub>-0.5 to EV<sub>DD</sub>-0.4, added DDR/bus output high/low voltage entries, removed load capacitance and DC injection current entries.</li> <li>Added filtering circuits and voltage sequencing sections: <a href="#">Section 5.4.1</a>, “PLL Power Filtering,” and <a href="#">Section 5.4.2</a>, “Supply Voltage Sequencing and Separation Cautions.”</li> <li>Removed “Operating Conditions” table from <a href="#">Section 5.5</a>, “Oscillator and PLL Electrical Characteristics,” since it is redundant with <a href="#">Table 7</a>.</li> <li><a href="#">Table 9</a>: Changed minimum core frequency to TBD, removed external reference and on-chip PLL frequency specs to have only a CLKOUT frequency spec of TBD to 83.33MHz, removed loss of reference frequency and self-clocked mode frequency entries, in EXTAL input high/low voltage entries changed “All other modes (Dual controller (1:1), Bypass, External)” to “All other modes (External, Limp)”, removed XTAL output high/low voltage entries, removed power-up to lock time entry, removed last 5 entries (frequency un-lock range, frequency lock range, CLKOUT period jitter, frequency modulation range limit, and ICO frequency)</li> </ul>
0.3	9/07/2005	<ul style="list-style-type: none"> <li>Corrected DRAMSEL footnote #3 in <a href="#">Table 3</a>.</li> <li>Updated <a href="#">Table 3</a> with 144MAPBGA pin locations.</li> <li>Added 144MAPBGA ballmap to <a href="#">Section 4.3</a>, “Pinout—144 MAPBGA.”</li> <li>Changed J12 from PLL_VDD to IVDD in <a href="#">Figure 9</a>.</li> </ul>
0.4	10/10/2005	<ul style="list-style-type: none"> <li><a href="#">Figure 1</a> and <a href="#">Table 3</a>: Changed pin 33 from EVDD to SD_VDD</li> <li><a href="#">Figure 4</a> and <a href="#">Table 3</a>: Changed ball D10 from TEST to VSS</li> <li><a href="#">Figure 6</a> and <a href="#">Table 3</a>: Changed pin 39 from EVDD to SD_VDD and pin 117 from TEST to VSS</li> </ul>
0.5	3/29/2006	<ul style="list-style-type: none"> <li>Added “top view” and “bottom view” labels where appropriate to mechanical drawings and pinouts.</li> <li>Updated mechanical drawings to latest available, and added note to <a href="#">Section 4</a>, “Mechanicals and Pinouts.”</li> </ul>

---

**THIS PAGE INTENTIONALLY LEFT BLANK**

## How to Reach Us:

### Home Page:

[www.freescale.com](http://www.freescale.com)

### E-mail:

[support@freescale.com](mailto:support@freescale.com)

### USA/Europe or Locations Not Listed:

Freescale Semiconductor  
Technical Information Center, CH370  
1300 N. Alma School Road  
Chandler, Arizona 85224  
+1-800-521-6274 or +1-480-768-2130  
[support@freescale.com](mailto:support@freescale.com)

### Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH  
Technical Information Center  
Schatzbogen 7  
81829 Muenchen, Germany  
+44 1296 380 456 (English)  
+46 8 52200080 (English)  
+49 89 92103 559 (German)  
+33 1 69 35 48 48 (French)  
[support@freescale.com](mailto:support@freescale.com)

### Japan:

Freescale Semiconductor Japan Ltd.  
Headquarters  
ARCO Tower 15F  
1-8-1, Shimo-Meguro, Meguro-ku,  
Tokyo 153-0064, Japan  
0120 191014 or +81 3 5437 9125  
[support.japan@freescale.com](mailto:support.japan@freescale.com)

### Asia/Pacific:

Freescale Semiconductor Hong Kong Ltd.  
Technical Information Center  
2 Dai King Street  
Tai Po Industrial Estate  
Tai Po, N.T., Hong Kong  
+800 2666 8080  
[support.asia@freescale.com](mailto:support.asia@freescale.com)

### For Literature Requests Only:

Freescale Semiconductor Literature Distribution Center  
P.O. Box 5405  
Denver, Colorado 80217  
1-800-441-2447 or 303-675-2140  
Fax: 303-675-2150  
[LDCForFreescaleSemiconductor@hibbertgroup.com](mailto:LDCForFreescaleSemiconductor@hibbertgroup.com)

Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.



Freescale™ and the Freescale logo are trademarks of Freescale Semiconductor, Inc. All other product or service names are the property of their respective owners. © Freescale Semiconductor, Inc. 2006. All rights reserved.

MCF5208EC  
Rev. 0.5  
3/2006